# GigaDevice Semiconductor Inc.

# GD32E503xx Arm® Cortex®-M33 32-bit MCU

**Datasheet** 

Revision 1.9

(Jul. 2023)



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#### 1. General description

The GD32E503xx device belongs to the high performance line of GD32 MCU family. It is a new 32-bit general-purpose microcontroller based on the Arm® Cortex®-M33 core. The Cortex®-M33 processor is a 32-bit processor that possesses low interrupt latency and low-cost debug. The characteristics of integrated and advanced make the Cortex®-M33 processor suitable for market products that require microcontrollers with high performance and low power consumption. The processor is based on the ARMv8 architecture and supports a powerful and scalable instruction set including general data processing I/O control tasks, advanced data processing bit field manipulations and DSP.

The GD32E503xx device incorporates the Arm® Cortex®-M3332-bit processor core operating at up to 180 MHz frequency with Flash accesses 0~4 waiting time to obtain maximum efficiency. It provides up to 512 KB embedded Flash memory and up to 128 KB SRAM memory. An extensive range of enhanced I/Os and peripherals connected to two APB buses. The devices offer three 12-bit ADCs, two DACs, up to nine general 16-bit timers, a general 32-bit timer, two basic timers, two PWM advanced timers, as well as standard and advanced communication interfaces: up to three SPIs, three I2Cs, six USARTs, two I2Ss, a SDIO, an USBD and two CANs. Additional peripherals as super high-resolution Timer (SHRTIMER), EXMC interface, Serial/Quad Parallel Interface (SQPI) are included.

The device operates from a 1.71 to 3.63 V power supply and available in -40 to +85 °C temperature range for grade 6 devices, -40 to +105 °C temperature range for grade 7 devices. Several power saving modes provide the flexibility for maximum optimization between wakeup latency and power consumption, an especially important consideration in low power applications.

The above features make the GD32E503xx devices suitable for a wide range of applications, especially in areas such as industrial control, motor drives, user interface, power monitor and alarm systems, consumer and handheld equipment, gaming and GPS, E-bike, optical module and so on.





## 2. Device overview

## 2.1. Device information

Table 2-1. GD32E503xx devices features and peripheral list

Part Number		GD32E503xx							
		СС	CE	RC	RE	VC	VE	ZC	ZE
I	FLASH (KB)	256	512	256	512	256	512	256	512
	SRAM (KB)	96	128	96	128	96	128	96	128
	General	3	9	3	9	3	9	3	9
	timer(16-bit)	(2-4)	(2-4,8-13)	(2-4)	(2-4,8-13)	(2-4)	(2-4,8-13)	(2-4)	(2-4,8-13)
	General	1	1	1	1	1	1	1	1
	timer(32-bit)	(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)
	Advanced	1	1	2	2	2	2	2	2
ers	timer(16-bit)	(0)	(0)	(0,7)	(0,7)	(0,7)	(0,7)	(0,7)	(0,7)
Timers	SysTick	1	1	1	1	1	1	1	1
	Basic	2	2	2	2	2	2	2	2
	timer(16-bit)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)	(5-6)
	SHRTIMER	1	1	1	1	1	1	1	1
	Watchdog	2	2	2	2	2	2	2	2
	RTC	1	1	1	1	1	1	1	1
	USART	3	3	4	4	4	4	4	4
		(0-2)	(0-2)	(0-2,5)	(0-2,5)	(0-2,5)	(0-2,5)	(0-2,5)	(0-2,5)
	UART	0	0	2	2	2	2	2	2
		O	O	(3-4)	(3-4)	(3-4)	(3-4)	(3-4)	(3-4)
itv	I2C	3	3	3	3	3	3	3	3
Connectivity		(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)	(0-2)
nne	SPI/I2S	3/2	3/2	3/2	3/2	3/2	3/2	3/2	3/2
ပိ		(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)	(0-2)/(1-2)
	SDIO	0	0	1	1	1	1	1	1
	CAN	2	2	2	2	2	2	2	2
	CAN	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)	(0-1)
	USBD	1	1	1	1	1	1	1	1
	GPIO	35	35	49	49	80	80	112	112
	EXMC	0	0	0	0	1	1	1	1
	DAC	2	2	2	2	2	2	2	2
O	11.14	3	3	3	3	3	3	3	3
. ≍I	Units								
ADC	Channels	10	10	16	16	16	16	21	21



## 2.2. Block diagram

SW/JTAG POR/PDR Code Flash ARM Cortex-M33 Memory Processor Fmax:180MHz PLL Fmax:180MHz Controller NVIC LDO FMC SQPI CRC RCU SDIO GP DMA 12 chs AHB Peripherals IRC 8MHz AHB Matrix SRAM Controller C SRAM EXMC HXTAL 4-32MHz AHB to APB AHB to APB Bridge2 Bridge1 LVD Interrput request Powered By VDDA USART0 USBD USART5 CAN0 SPI0 WWDGT 12-bit ADC0~2 SAR ADC TIMER1~3 EXTI GPIOA USART1~2 GPIOB I2C0~2 GPIOC I2C2 GPIOD FWDGT GPIOE RTC GPIOF DAC GPIOG TIMER4~6 TIMER0 UART3~4 TIMER7 CAN1 TIMER8~10 TIMER 11~13 SHRTIMER ( СТС

Figure 2-1. GD32E503xx block diagram



#### 2.3. Pinouts and pin assignment

Figure 2-2. GD32E503Zx LQFP144 pinouts

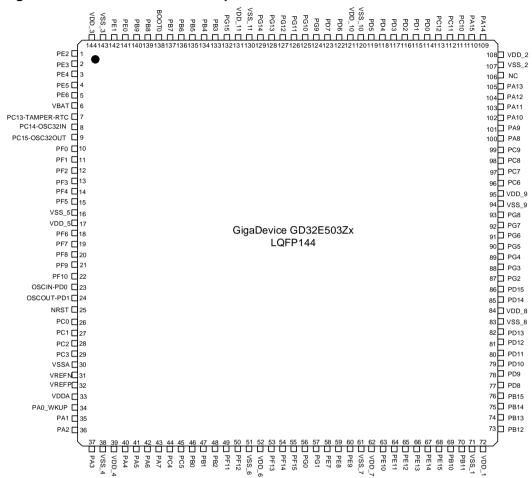




Figure 2-3. GD32E503Vx LQFP100 pinouts

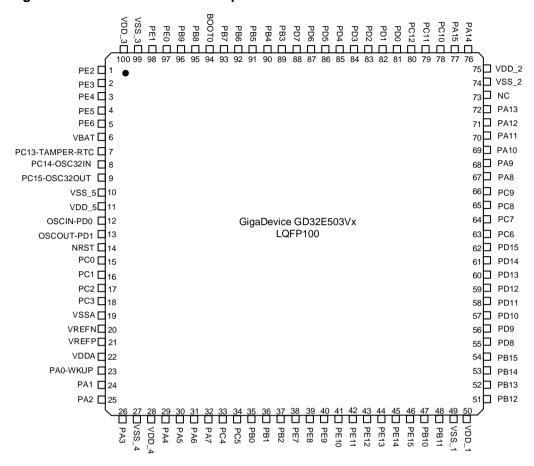




Figure 2-4. GD32E503Rx LQFP64 pinouts

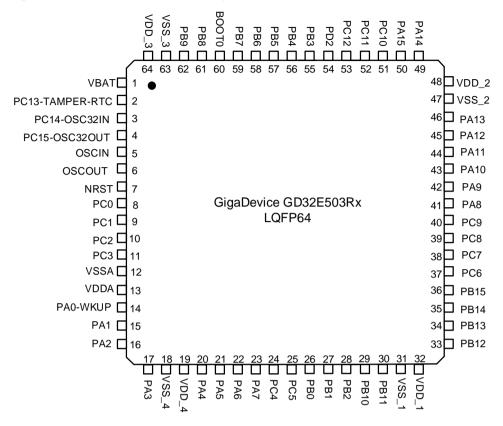
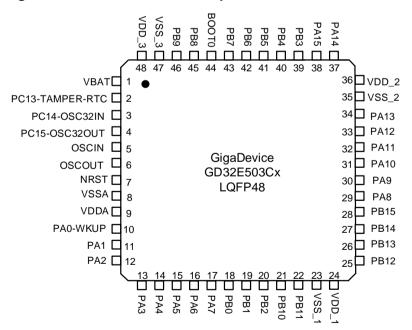


Figure 2-5. GD32E503Cx LQFP48 pinouts





## 2.4. Memory map

Table 2-2. GD32E503xx memory map

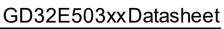
Pre-defined	ZECOCX	x memory map	
Regions	Bus	Address	Peripherals
		0xC000 0000 - 0xDFFF FFFF	Reserved
		0xB000 0000 - 0xBFFF FFFF	SQPI_PSRAM(MEM)
External		0xA000 1400 - 0xAFFF FFFF	Reserved
device		0xA000 1000 - 0xA000 13FF	SQPI_PSRAM(REG)
	AHB3	0xA000 0000 - 0xA000 0FFF	EXMC - SWREG
		0x9000 0000 - 0x9FFF FFFF	EXMC - PC CARD
		0x7000 0000 - 0x8FFF FFFF	EXMC - NAND
External RAM		0x6000 0000 - 0x6FFF FFFF	EXMC -
			NOR/PSRA M/SRA M
		0x5000 0000 - 0x5003 FFFF	Reserved
		0x4008 0400 - 0x4FFF FFFF	Reserved
		0x4008 0000 - 0x4008 03FF	Reserved
		0x4004 0000 - 0x4007 FFFF	Reserved
		0x4002 BC00 - 0x4003 FFFF	Reserved
		0x4002 B000 - 0x4002 BBFF	Reserved
		0x4002 A000 - 0x4002 AFFF	Reserved
		0x4002 8000 - 0x4002 9FFF	Reserved
		0x4002 6800 - 0x4002 7FFF	Reserved
		0x4002 6400 - 0x4002 67FF	Reserved
		0x4002 6000 - 0x4002 63FF	Reserved
		0x4002 5000 - 0x4002 5FFF	Reserved
		0x4002 4000 - 0x4002 4FFF	Reserved
Peripheral	AHB1	0x4002 3C00 - 0x4002 3FFF	Reserved
renpheral		0x4002 3800 - 0x4002 3BFF	Reserved
		0x4002 3400 - 0x4002 37FF	Reserved
		0x4002 3000 - 0x4002 33FF	CRC
		0x4002 2C00 - 0x4002 2FFF	Reserved
		0x4002 2800 - 0x4002 2BFF	Reserved
		0x4002 2400 - 0x4002 27FF	Reserved
		0x4002 2000 - 0x4002 23FF	FMC
		0x4002 1C00 - 0x4002 1FFF	Reserved
		0x4002 1800 - 0x4002 1BFF	Reserved
		0x4002 1400 - 0x4002 17FF	Reserved
		0x4002 1000 - 0x4002 13FF	RCU
		0x4002 0C00 - 0x4002 0FFF	Reserved
1			
		0x4002 0800 - 0x4002 0BFF	Reserved



Pre-defined			
Regions	Bus	Address	Peripherals
		0x4002 0000 - 0x4002 03FF	DMA0
		0x4001 8400 - 0x4001 FFFF	Reserved
		0x4001 8000 - 0x4001 83FF	SDIO
		0x4001 7C00 - 0x4001 7FFF	Reserved
		0x4001 7800 - 0x4001 7BFF	Reserved
		0x4001 7400 - 0x4001 77FF	SHRTIMER
		0x4001 7000 - 0x4001 73FF	USART5
		0x4001 6C00 - 0x4001 6FFF	Reserved
		0x4001 6800 - 0x4001 6BFF	Reserved
		0x4001 5C00 - 0x4001 67FF	Reserved
		0x4001 5800 - 0x4001 5BFF	Reserved
		0x4001 5400 - 0x4001 57FF	TIMER10
		0x4001 5000 - 0x4001 53FF	TIMER9
		0x4001 4C00 - 0x4001 4FFF	TIMER8
		0x4001 4800 - 0x4001 4BFF	Reserved
		0x4001 4400 - 0x4001 47FF	Reserved
		0x4001 4000 - 0x4001 43FF	Reserved
	A DD0	0x4001 3C00 - 0x4001 3FFF	ADC2
	APB2	0x4001 3800 - 0x4001 3BFF	USART0
		0x4001 3400 - 0x4001 37FF	TIMER7
		0x4001 3000 - 0x4001 33FF	SPI0
		0x4001 2C00 - 0x4001 2FFF	TIMER0
		0x4001 2800 - 0x4001 2BFF	ADC1
		0x4001 2400 - 0x4001 27FF	ADC0
		0x4001 2000 - 0x4001 23FF	GPIOG
		0x4001 1C00 - 0x4001 1FFF	GPIOF
		0x4001 1800 - 0x4001 1BFF	GPIOE
		0x4001 1400 - 0x4001 17FF	GPIOD
		0x4001 1000 - 0x4001 13FF	GPIOC
		0x4001 0C00 - 0x4001 0FFF	GPIOB
		0x4001 0800 - 0x4001 0BFF	GPIOA
		0x4001 0400 - 0x4001 07FF	EXTI
		0x4001 0000 - 0x4001 03FF	AFIO
		0x4000 CC00 - 0x4000 FFFF	Reserved
		0x4000 CC00 - 0x4000 CFFF	Reserved
		0x4000 C800 - 0x4000 CBFF	СТС
	APB1	0x4000 C400 - 0x4000 C7FF	Reserved
		0x4000 C000 - 0x4000 C3FF	l2C2
		0x4000 8C00 - 0x4000 BFFF	Reserved
		0x4000 8800 - 0x4000 8BFF	Reserved



Pre-defined			BOZEGOOXAD
Regions Bus		Address	Peripherals
		0x4000 8400 - 0x4000 87FF	USBSRAM_B
		0x4000 8000 - 0x4000 BFFF	Reserved
		0x4000 7C00 - 0x4000 7FFF	Reserved
		0x4000 7800 - 0x4000 7BFF	Reserved
		0x4000 7400 - 0x4000 77FF	DAC
		0x4000 7000 - 0x4000 73FF	PMU
		0x4000 6C00 - 0x4000 6FFF	BKP
		0x4000 6800 - 0x4000 6BFF	CAN1
		0x4000 6400 - 0x4000 67FF	CA NO
		0x4000 6000 - 0x4000 63FF	Shared USBD/CAN SRAM 512 bytes
		0x4000 5C00 - 0x4000 5FFF	USBD
		0x4000 5800 - 0x4000 5BFF	I2C1
		0x4000 5400 - 0x4000 57FF	I2C0
		0x4000 5000 - 0x4000 53FF	UART4
		0x4000 4C00 - 0x4000 4FFF	UART3
		0x4000 4800 - 0x4000 4BFF	USART2
		0x4000 4400 - 0x4000 47FF	USART1
		0x4000 4000 - 0x4000 43FF	l2S2_add
		0x4000 3C00 - 0x4000 3FFF	SPI2/I2S2
		0x4000 3800 - 0x4000 3BFF	SPI1/I2S1
		0x4000 3400 - 0x4000 37FF	I2S1_add
		0x4000 3000 - 0x4000 33FF	FWDGT
		0x4000 2C00 - 0x4000 2FFF	WWDGT
		0x4000 2800 - 0x4000 2BFF	RTC
		0x4000 2400 - 0x4000 27FF	Reserved
		0x4000 2000 - 0x4000 23FF	TIMER13
		0x4000 1C00 - 0x4000 1FFF	TIMER12
		0x4000 1800 - 0x4000 1BFF	TIMER11
		0x4000 1400 - 0x4000 17FF	TIMER6
		0x4000 1000 - 0x4000 13FF	TIMER5
		0x4000 0C00 - 0x4000 0FFF	TIMER4
		0x4000 0800 - 0x4000 0BFF	TIMER3
		0x4000 0400 - 0x4000 07FF	TIMER2
		0x4000 0000 - 0x4000 03FF	TIMER1
		0x2007 0000 - 0x3FFF FFFF	Reserved
		0x2006 0000 - 0x2006 FFFF	Reserved
SRAM	AHB	0x2003 0000 - 0x2005 FFFF	Reserved
		0x2002 0000 - 0x2002 FFFF	Reserved
		0x2000 0000 - 0x2001 FFFF	SRAM



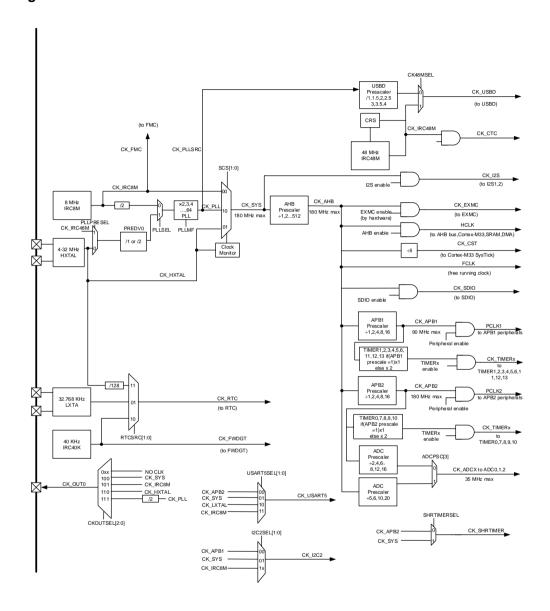


			BOZEGOOMB	
Pre-defined Regions	Bus	Address	Peripherals	
		0x1FFF F810 - 0x1FFF FFFF	Reserved	
		0x1FFF F800 - 0x1FFF F80F	Option Bytes	
		0x1FFF E000 - 0x1FFF F7FF	Boot loader	
		0x1FFF 7800 - 0x1FFF DFFF	Reserved	
		0x1FFF 7000 - 0x1FFF 77FF	OTP	
		0x1FFF 0000 - 0x1FFF 6FFF	Reserved	
	АНВ	0x1FFE C010 - 0x1FFE FFFF	Reserved	
		0x1FFE C000 - 0x1FFE C00F	Reserved	
		0x1001 0000 - 0x1FFE BFFF	Reserved	
Code		AHB	0x1000 0000 - 0x1000 FFFF	Reserved
			0x083C 0000 - 0x0FFF FFFF	Reserved
		0x0830 0000 - 0x083B FFFF	Reserved	
		0x0808 0000 - 0x082F FFFF	Reserved	
		0x0800 0000 - 0x0807 FFFF	Main Flash	
		0x0030 0000 - 0x07FF FFFF	Reserved	
		0x0010 0000 - 0x002F FFFF	Reserved	
		0x0008 0000 - 0x000F FFFF	Reserved	
		0x0002 0000 - 0x0007 FFFF	Aliased to Main Flash	
		0x0000 0000 - 0x0001 FFFF	or Boot loader	



#### 2.5. Clock tree

Figure 2-6. GD32E503xx clock tree



#### Note

The TIMERs are clocked by the clock divided from CK\_APB2 and CK\_APB1. The frequency of TIMERs clock is equal to CK\_APBx(APB prescaler is 1), twice the CK\_APBx(APB prescaler is not 1).

#### Legend:

HXTAL: High speed crystal oscillator LXTAL: Low speed crystal oscillator IRC8M: Internal 8M RC oscillator IRC40K: Internal 40K RC oscillator IRC48M: Internal 48M RC oscillator



### 2.6. Pin definitions

#### 2.6.1. GD32E503Zx LQFP144 pin definitions

Table 2-3. GD32E503Zx LQFP144 pin definitions

	Table 2-3. GD32E503Zx LQFP144 pin definitions  GD32E503Zx LQFP144						
Pin Name Pins Pin I/O Functions description <sup>(3)</sup>			Functions description(3)				
riii Naiile	FIIIS	Type <sup>(1)</sup>	Level <sup>(2)</sup>	runctions description			
PE2	1	VO	5VT	Default: PE2 Alternate2: EXMC_A23			
PE3	2	VO	5VT	Default: PE3 Alternate2: EXMC_A19			
PE4	3	VO	5VT	Default: PE4 Alternate2: EXMC_A20			
PE5	4	VO	5VT	Default: PE5 Alternate2: EXMC_A21 Remap: TIMER8_CH0 <sup>(4)</sup>			
PE6	5	VO	5VT	Default: PE6 Alternate2: EXMC_A22, WKUP2 Remap: TIMER8_CH1 <sup>(4)</sup>			
VBAT	6	Р		Default: VBAT			
PC13- TAMPER- RTC	7	VO		Default: PC13 Alternate2: TAMPER-RTC, WKUP1			
PC14- OSC32IN	8	VO		Default: PC14 Alternate2: OSC32IN			
PC15- OSC32OUT	9	VO		Default: PC15 Alternate2: OSC32OUT			
PF0	10	VO	5VT	Default: PF0 Alternate2: EXMC_A0, SQPI_D0 Remap: CTC_SYNC			
PF1	11	VO	5VT	Default: PF1 Alternate2: EXMC_A1			
PF2	12	VO	5VT	Default: PF2 Alternate2: EXMC_A2, SQPI_D2			
PF3	13	VO	5VT	Default: PF3 Alternate2: EXMC_A3			
PF4	14	VO	5VT	Default: PF4 Alternate2: EXMC_A4, SQPI_D1			
PF5	15	VO	5VT	Default: PF5 Alternate2: EXMC_A5			
VSS_5	16	Р		Default: VSS_5			
VDD_5	17	Р		Default: VDD_5			
PF6	18	VO		Default: PF6 Alternate2: ADC2_IN4, EXMC_NIORD, SQPI_CSN			



	GD32E503Zx LQFP144						
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
		Type	Leven	Remap: TIMER9_CH0 <sup>(4)</sup>			
				Default: PF7			
PF7	19	VO		Alternate2: ADC2_IN5, EXMC_NREG			
,	13			Remap: TIMER10_CH0 <sup>(4)</sup>			
				Default: PF8			
D=0				Alternate2: ADC2_IN6, EXMC_NIOWR, WKUP7,			
PF8	20	VO		SQPLCLK			
				Remap: TIMER12_CH0 <sup>(4)</sup>			
				Default: PF9			
PF9	21	VO		Alternate2: ADC2_IN7, EXMC_CD			
				Remap: TIMER13_CH0 <sup>(4)</sup>			
PF10	22	VO		Default: PF10			
				Alternate2: ADC2_IN8, EXMC_INTR, SQPI_D3			
OSCIN-PD0	23	1		Default: OSCIN			
OSCOUT-				Remap: PD0 Default: OSCOUT			
	24	0					
PD1	25	1/0		Remap: PD1			
NRST	25	VO		Default: NRST Default: PC0			
PC0	26	VO		Alternate2: ADC012_IN10			
				Default: PC1			
PC1	27	VO		Alternate2: ADC012_IN11			
				Default: PC2			
PC2	28	VO		Alternate1: I2S1_ADD_SD			
				Alternate2: ADC012_IN12			
PC3	29	VO		Default: PC3			
-ω	29	10		Alternate2: ADC012_IN13			
VSSA	30	Р		Default: VSSA			
VREFN	31	Р		Default: VREFN			
VREFP	32	Р		Default: VREFP			
V DDA	33	Р		Default: VDDA			
				Default: PA0			
PA0-WKUP	34	VO		Alternate2: WKUP0, USART1_CTS, ADC012_IN0,			
17to vitoi	01			TIMER1_CH0, TIMER1_ETI, TIMER4_CH0,			
				TIMER7_ETI			
D. 4	0.5	1/0		Default: PA1			
PA1	35	VO		Alternate2: USART1_RTS, ADC012_IN1,			
				TIMER4_CH1, TIMER1_CH1 Default: PA2			
PA2	36	VO		Alternate2: USART1_TX, TIMER4_CH2, ADC012_IN2,			
FA4	30			TIMER8_CH0 <sup>(4)</sup> , TIMER1_CH2, SPI0_IO2, WKUP3			
				Default: PA3			
PA3	37	VO		Alternate2: USART1_RX, TIMER4_CH3, ADC012_IN3,			
				TIMER1_CH3, TIMER8_CH1 <sup>(4)</sup> , SPI0_IO3			



GD32E503Zx LQFP144							
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
VSS_4	38	P	Leven	Default: VSS_4			
VDD_4	39	P		Default: VDD 4			
V DD_4	39	<u> </u>		Default: PA4			
				Alternate2: SPI0_NSS, USART1_CK, DAC_OUT0,			
PA4	40	VO		ADC01 IN4			
				Remap: SPI2_NSS, I2S2_WS			
				Default: PA5			
PA5	41	VO		Alternate2: SPI0_SCK, ADC01_IN5, DAC_OUT1			
				Default: PA6			
DA O	40	1/0		Alternate2: SPI0_MISO, TIMER7_BRKIN, ADC01_IN6,			
PA6	42	VO		TIMER2_CH0, TIMER12_CH0 <sup>(4)</sup>			
				Remap: TIMER0_BRKIN			
				Default: PA7			
PA7	43	VO		Alternate2: SPI0_MOSI, TIMER7_CH0_ON,			
PA1	43			ADC01_IN7, TIMER2_CH1, TIMER13_CH0 <sup>(4)</sup>			
				Remap: TIMER0_CH0_ON			
PC4	44	VO		Default: PC4			
104	44	70		Alternate2: ADC01_IN14			
PC5	45	VO		Default: PC5			
100	70	70		Alternate2: ADC01_IN15, WKUP4			
				Default: PB0			
PB0	46	VO		Alternate2: ADC01_IN8, TIMER2_CH2,			
1 20	10			TIMER7_CH1_ON			
				Remap: TIMER0_CH1_ON			
				Default: PB1			
				Alternate1: SHRTIMER_SCOUT			
PB1	47 VO	7 VO		Alternate2: ADC01_IN9, TIMER2_CH3,			
				TIMER7_CH2_ON			
				Remap: TIMER0_CH2_ON			
PB2	48	VO	5VT	Default: PB2, BOOT1			
				Alternate1: SHRTIMER_SCIN			
PF11	49	VO	5VT	Default: PF11			
				Alternate2: EXMC_NIOS16			
PF12	50	VO	5VT	Default: PF12			
V60 0	F.4			Alternate2: EXMC_A6			
VSS_6	51	P		Default: VSS_6			
VDD_6	52	Р		Default: VDD_6			
PF13	53	VO	5VT	Default: PF13			
				Alternate2: EXMC_A7			
PF14	54	VO	5VT	Default: PF14			
		<del> </del>		Alternate2: EXMC_A8			
PF15	55	VO	5VT	Default: PF15 Alternate2: EXMC_A9			
DCO	EG	1/0	E\/T				
PG0	56	<i>V</i> O	5VT	Default: PG0			



GD32E303XX DataSHE							
		Pin	1/0	LLUOULA LOUI 1777			
Pin Name	Pins	Type <sup>(1)</sup>	Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
				Alternate2: EXMC_A10			
PG1 57	57	<i>V</i> O	5VT	Default: PG1			
	57	10	371	Alternate2: EXMC_A11			
				Default: PE7			
PE7	58	VO	5VT	Alternate2: EXMC_D4			
				Remap: TIMER0_ETI			
				Default: PE8			
PE8	59	VO	5VT	Alternate2: EXMC_D5			
				Remap: TIMER0_CH0_ON			
D=0			-> /	Default: PE9			
PE9	60	VO	5VT	Alternate2: EXMC_D6			
\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\				Remap: TIMERO_CH0			
VSS_7	61	P _		Default: VSS_7			
VDD_7	62	Р		Default: VDD_7			
				Default: PE10			
PE10	63	VO	5VT	Alternate2: EXMC_D7			
				Remap: TIMER0_CH1_ON			
		64 VO		Default: PE11			
PE11	64			Alternate2: EXMC_D8			
				Remap: TIMER0_CH1			
		VO	5VT	Default: PE12			
PE12	65			Alternate2: EXMC_D9			
				Remap: TIMER0_CH2_ON			
DE4.0	00		5VT	Default: PE13			
PE13	66	VO		Alternate2: EXMC_D10			
				Remap: TIMERO_CH2			
DE4.4	67	1/0	EV/T	Default: PE14			
PE14	67	VO	5VT	Alternate2: EXMC_D11 Remap: TIMER0_CH3			
				Default: PE15			
PE15	68	VO	5\/T	Alternate2: EXMC D12			
1 1 1 1 1 1	00		5VT	Remap: TIMERO_BRKIN			
				Default: PB10			
				Alternate1: SHRTIMER FLT2			
PB10	69	VO	5VT	Alternate2: I2C1_SCL, USART2_TX			
				Remap: TIMER1_CH2			
		1		Default: PB11			
				Alternate1: SHRTIMER_FLT3			
PB11	70	VO	5VT	Alternate2: I2C1_SDA, USART2_RX			
				Remap: TIMER1_CH3			
VSS_1	71	Р		Default: VSS_1			
VDD_1	72	P		Default: VDD_1			
, , , , , ,		<u> </u>		Default: PB12			
PB12	73	VO	5VT	Alternate1: SHRTIMER_ST2CH0			
				/ Mornato I. OF INTHINIEN_O 12 OF IO			



GD32E503Zx LQFP144							
Pin Name	Pins	Pin	I/O	Functions description <sup>(3)</sup>			
I III INAIIIE	1 1113	Type <sup>(1)</sup>	Level <sup>(2)</sup>	rundions description			
				Alternate2: SPI1_NSS, I2S1_WS, I2C1_SMBA,			
				USART2_CK, TIMER0_BRKIN, CAN1_RX			
				Default: PB13			
PB13	74	VO	5VT	Alternate1: SHRTIMER_ST2CH1			
12.0			0.1	Alternate2: SPI1_SCK, I2S1_CK, USART2_CTS,			
				TIMER0_CH0_ON, CAN1_TX, I2C1_TX FRA ME			
				Default: PB14			
PB14	75	VO	5VT	Alternate1: SHRTIMER_ST3CH0, I2S1_ADD_SD			
				Alternate2: SP1_MISO, USART2_RTS,			
				TIMERO_CH1_ON, TIMER11_CH0 <sup>(4)</sup>			
				Default: PB15			
PB15	76	VO	5VT	Alternate1: SHRTIMER_ST3CH1			
				Alternate2: SPI1_MOSI, TIMER0_CH2_ON, I2S1_SD, TIMER11_CH1 <sup>(4)</sup> , WKUP6			
				Default: PD8			
PD8	77	VO	5VT	Alternate2: EXMC_D13			
120			3 1	Remap: USART2_TX			
				Default: PD9			
PD9	78	VO	5VT	Alternate2: EXMC_D14			
				Remap: USART2_RX			
				Default: PD10			
PD10	79	VO	5VT	Alternate2: EXMC_D15			
				Remap: USART2_CK			
		VO	5VT	Default: PD11			
PD11	80			Alternate2: EXMC_A16/EXMC_CLE			
				Remap: USART2_CTS			
				Default: PD12			
PD12	81	VO	5VT	Alternate2: EXMC_A17/EXMC_ALE			
				Remap: TIMER3_CH0, USART2_RTS			
				Default: PD13			
PD13	82	VO.	5VT	Alternate2: EXMC_A18			
\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\				Remap: TIMER3_CH1			
VSS_8	83	P		Default: VSS_8			
VDD_8	84	Р		Default: VDD_8			
	<b></b>		<i>-</i> -	Default: PD14			
PD14	85	VO.	5VT	Alternate2: EXMC_D0			
				Remap: TIMER3_CH2			
DD4E	90	1/0	E\/T	Default: PD15 Alternate2: EXMC_D1			
PD15	86	VO	5VT	Remap: TIMER3_CH3, CTC_SYNC			
				Default: PG2			
PG2	87	VO	5VT	Alternate2: EXMC_A12			
				Default: PG3			
PG3	88	VO	5VT	Alternate2: EXMC_A13			



	GD32E303XX DataStree						
	<u> </u>			2E3032X			
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
PG4	89	VO	5VT	Default: PG4 Alternate2: EXMC_A14, SQPI_CSN			
				Default: PG5			
PG5	90	VO	5VT	Alternate2: EXMC_A15			
				Default: PG6			
PG6	91	VO	5VT	Alternate1: SHRTIMER_ST4CH0			
				Alternate2: EXMC_INT1, SQPI_D1			
				Default: PG7			
PG7	92	VO	5VT	Alternate1: SHRTIMER_ST4CH1, USART5_CK			
				Alternate2: EXMC_INT2			
DCo	02	1/0	5VT	Default: PG8			
PG8	93	VO	571	Alternate2: SQPI_D2			
VSS_9	94	Р		Default: VSS_9			
VDD_9	95	Р		Default: VDD_9			
				Default: PC6			
200			-> /	Alternate1: SHRTIMER_EXEV9, USART5_TX			
PC6	96	VO	5VT	Alternate2: I2S1_MCK, TIMER7_CH0, SDIO_D6			
				Remap: TIMER2_CH0			
				Default: PC7			
		7 VO	_,,_	Alternate1: SHRTIMER_FLT4, USART5_RX			
PC7	97		5VT	Alternate2: I2S2_MCK, TIMER7_CH1, SDIO_D7			
				Remap: TIMER2_CH1			
				Default: PC8			
DO0	00	1/0	5) /T	Alternate1: SHRTIMER_ST4CH0, USART5_CK			
PC8	98	VO	5VT	Alternate2: TIMER7_CH2, SDIO_D0			
				Remap: TIMER2_CH2			
				Default: PC9			
DO0	00	1/0	5VT	Alternate1: SHRTIMER_ST4CH1, I2C2_SDA			
PC9	99	VO		Alternate2: TIMER7_CH3, SDIO_D1			
				Remap: TIMER2_CH3			
				Default: PA8			
DA O	400	1/0	5\/T	Alternate1: SHRTIMER_ST0CH0, I2C2_SCL			
PA8	100	VO	5VT	Alternate2: USART0_CK, TIMER0_CH0, CK_OUT,			
				CTC_SYNC			
				Default: PA9			
PA9	101	VO	5VT	Alternate1: SHRTIMER_ST0CH1, I2C2_SMBA			
				Alternate2: USART0_TX, TIMER0_CH1			
PA10 1				Default: PA10			
	102	VO	5VT	Alternate1: SHRTIMER_ST1CH0			
				Alternate2: USART0_RX, TIMER0_CH2			
				Default: PA11			
DA 44	400	1/0		Alternate1: SHRTIMER_ST1CH1, USART5_TX			
PA11	103	VO		Alternate2: USART0_CTS, CAN0_RX,USBDM,			
				TIMER0_CH3			



GD32E503Zx LQFP144							
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
PA12	104	VO		Default: PA12 Alternate1: SHRTIMER_FLT0, USART5_RX Alternate2: USART0_RTS, CAN0_TX, USBDP, TIMER0_ETI			
PA13	105	VO	5VT	Default: JTMS, SWDIO Remap: PA13			
NC	106			-			
VSS_2	107	Р		Default: VSS_2			
VDD_2	108	Р		Default: VDD_2			
PA14	109	VO	5VT	Default: JTCK, SWCLK Remap: PA14			
PA15	110	VO	5VT	Default: JTDI Alternate1: SHRTIMER_FLT1 Alternate2: SPI2_NSS, I2S2_WS Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS			
PC10	111	VO	5VT	Default: PC10 Alternate1: I2C2_SCL Alternate2: UART3_TX, SDIO_D2 Remap: USART2_TX, SPI2_SCK, I2S2_CK			
PC11	112	VO	5VT	Default: PC11 Alternate1: SHRTIMER_EXEV1, I2S2_ADD_SD Alternate2: UART3_RX, SDIO_D3 Remap: USART2_RX, SPI2_MISO			
PC12	113	VO	5VT	Default: PC12 Alternate1: SHRTIMER_EXEV0 Alternate2: UART4_TX, SDIO_CK Remap: USART2_CK, SPI2_MOSI, I2S2_SD			
PD0	114	l/O	5VT	Default: PD0 Alternate2: EXMC_D2 Remap: CAN0_RX			
PD1	115	l/O	5VT	Default: PD1 Alternate2: EXMC_D3 Remap: CAN0_TX			
PD2	116	VO	5VT	Default: PD2 Alternate2: TIMER2_ETI, UART4_RX, SDIO_CMD			
PD3	117	VO	5VT	Default: PD3 Alternate2: EXMC_CLK Remap: USART1_CTS			
PD4	118	VO	5VT	Default: PD4 Alternate1: SHRTIMER_FLT2 Alternate2: EXMC_NOE Remap: USART1_RTS			
PD5	119	VO	5VT	Default: PD5 Alternate1: SHRTIMER_EXEV2			



	GD32E303XX DataSHE							
		Pin	1/0	ZEDUZZA EQIF144				
Pin Name	Pins	Type <sup>(1)</sup>	Level <sup>(2)</sup>	Functions description <sup>(3)</sup>				
				Alternate2: EXMC_NWE				
				Remap: USART1_TX				
VSS_10	120			Default: VSS_10				
VDD_10	121			Default: VDD_10				
				Default: PD6				
PD6	122	VO	5VT	Alternate2: EXMC_NWAIT				
				Remap: USART1_RX				
				Default: PD7				
PD7	123	VO	5VT	Alternate2: EXMC_NE0, EXMC_NCE1				
				Remap: USART1_CK				
				Default: PG9				
PG9	124	VO	5VT	Alternate1: USART5_RX				
				Alternate2: EXMC_NE1, EXMC_NCE2				
				Default: PG10				
PG10	125	VO	5VT	Alternate1: SHRTIMER_FLT4				
				Alternate2: EXMC_NCE3_0, EXMC_NE2				
				Default: PG11				
PG11	126	VO	5VT	Alternate1: SHRTIMER_EXEV3				
				Alternate2: EXMC_NCE3_1				
			5VT	Default: PG12				
PG12	127	VO		Alternate1: SHRTIMER_EXEV4				
				Alternate2: EXMC_NE3				
				Default: PG13				
PG13	128	VO	5VT	Alternate1: SHRTIMER_EXEV9				
				Alternate2: EXMC_A24				
		1/0	_,	Default: PG14				
PG14	129	VO	5VT	Alternate1: USART5_TX				
				Alternate2: EXMC_A25				
VSS_11	130	Р		Default: VSS_11				
VDD_11	131	Р		Default: VDD_11				
PG15	132	VO	5VT	Default: PG15				
				Default: JTDO				
PB3	133	VO	5VT	Alternate1: SHRTIMER_SCOUT, SHRTIMER_EXEV8				
1 50	100		0 1	Alternate2: SPI2_SCK, I2S2_CK				
				Remap: TIMER1_CH1, PB3, SPI0_SCK, TRACESWO				
				Default: NJTRST				
PB4 134				Alternate1: SHRTIMER_EXEV6, I2C2_SDA,				
	134	VO	5VT	I2S2_ADD_SD				
				Alternate2: SPI2_MISO, I2C0_TXFRAME				
				Remap: TIMER2_CH0, PB4, SPI0_MISO				
				Default: PB5				
PB5	135	VO		Alternate1: SHRTIMER_EXEV5, I2C2_SCL				
. 50		70		Alternate2: I2C0_SMBA, SPI2_MOSI, I2S2_SD,				
				WKUP5				



	GD32E503Zx LQFP144							
Pin Name	Pins	Pin	1/0	Functions description <sup>(3)</sup>				
riii Naiile	FIIIS	Type <sup>(1)</sup>	Level <sup>(2)</sup>	runctions description				
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX				
				Default: PB6				
PB6	136	VO	5VT	Alternate1: SHRTIMER_SCIN, SHRTIMER_EXEV3				
PD0	130	10	301	Alternate2: I2C0_SCL, TIMER3_CH0				
				Remap: USART0_TX, CAN1_TX, SPI0_IO2				
				Default: PB7				
PB7	137	VO	5VT	Alternate1: SHRTIMER_EXEV2				
PD/	137	100	501	Alternate2: I2C0_SDA , TIMER3_CH1, EXMC_NA DV				
				Remap: USART0_RX, SPI0_IO3				
BOOT0	138	I		Default: BOOT0				
				Default: PB8				
DDO	139	1/0	5VT	Alternate1: SHRTIMER_EXEV7, I2C2_SDA				
PB8	139	VO.	501	Alternate2: TIMER3_CH2, SDIO_D4, TIMER9_CH0 <sup>(4)</sup>				
				Remap: I2C0_SCL, CAN0_RX				
				Default: PB9				
PB9	140	VO	5VT	Alternate1: SHRTIMER_EXEV4				
PD9	140	100	501	Alternate2: TIMER3_CH3, SDIO_D5, TIMER10_CH0 <sup>(4)</sup>				
				Remap: I2C0_SDA, CAN0_TX				
				Default: PE0				
PE0	141	VO	5VT	Alternate1: SHRTIMER_SCIN				
				Alternate2: TIMER3_ETI, EXMC_NBL0				
				Default: PE1				
PE1	142	VO	5VT	Alternate1: SHRTIMER_SCOUT				
				Alternate2: EXMC_NBL1				
VSS_3	143	Р		Default: VSS_3				
VDD_3	144	Р		Default: VDD_3				

#### Notes:

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Alternate1: The specified function can be mapped to the specific pin by configuring AFIO\_PCFA ~ AFIO\_PCFG registers.
  - Alternate2: These functions can be enabled with correct GPIO and function module mode configurations.
  - Remap: A group of the specified module functions can be mapped to the specified pins by configuring AFIO\_PCF0 ~ AFIO\_PCF1 registers.
- (4) Functions are available in GD32E503xE devices.



### 2.6.2. GD32E503Vx LQFP100 pin definitions

Table 2-4. GD32E503Vx LQFP100 pin definitions

	GD32E503VX LQFP100 pin definitions					
		Pin	I/O	(0)		
Pin Name	Pins	Type <sup>(1)</sup>	Level <sup>(2)</sup>	Functions description <sup>(3)</sup>		
DEO	1	VO	5VT	Default: PE2		
PE2	1	10	501	Alternate2: EXMC_A23		
PE3	2	VO	5VT	Default: PE3		
. =0	_			Alternate2: EXMC_A19		
PE4	3	VO	5VT	Default: PE4		
				Alternate2: EXMC_A20 Default: PE5		
PE5	4	VO	5VT	Alternate2: EXMC_A21		
120	7			Remap: TIMER8_CH0 <sup>(4)</sup>		
				Default: PE6		
PE6	5	VO	5VT	Alternate2: EXMC_A22, WKUP2		
				Remap: TIMER8_CH1 <sup>(4)</sup>		
VBAT	6	Р		Default: VBAT		
PC13-						
TAMPER-	7	VO		Default: PC13		
RTC				Alternate2: TAMPER-RTC, WKUP1		
PC14-				Default: PC14		
OSC32IN	8	VO		Alternate2: OSC32IN		
PC15-				Default: PC15		
OSC32OUT	9	VO		Alternate2: OSC32OUT		
VSS_5	10	Р		Default: VSS_5		
VDD_5	11	Р		Default: VDD_5		
OSCIN-PD0	12			Default: OSCIN		
OSCIN-FD0	12	'		Remap: PD0		
OSCOUT-	13	0		Default: OSCOUT		
PD1	15	Ŭ		Remap: PD1		
NRST	14	VO		Default: NRST		
PC0	15	VO		Default: PC0		
100	10	,,,		Alternate2: ADC012_IN10		
PC1	16	VO		Default: PC1		
				Alternate2: ADC012_IN11		
500				Default: PC2		
PC2	17	VO.		Alternate1: I2S1_ADD_SD		
				Alternate2: ADC012_IN12		
PC3	18	VO		Default: PC3 Alternate2: ADC012_IN13		
VSSA	19	Р		Default: VSSA		
VREFN	20	P		Default: VREFN		
VREFP	21	Р		Default: VREFP		
VDDA	22	P		Default: VDDA		
V DDA	~~	[ F	Ī	Doraul. V DDA		



	GD32E503Vx LQFP100						
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
PA0-WKUP	23	VO		Default: PA0 Alternate2: WKUP0, USART1_CTS, ADC012_IN0, TIMER1_CH0, TIMER1_ETI, TIMER4_CH0, TIMER7_ETI			
PA1	24	VO		Default: PA1 Alternate2: USART1_RTS, ADC012_IN1, TIMER4_CH1, TIMER1_CH1			
PA2	25	VO		Default: PA2 Alternate2: USART1_TX, TIMER4_CH2, ADC012_IN2, TIMER8_CH0 <sup>(4)</sup> , TIMER1_CH2, SPI0_IO2, WKUP3			
PA3	26	VO		Default: PA3 Alternate2: USART1_RX, TIMER4_CH3, ADC012_IN3, TIMER1_CH3, TIMER8_CH1 <sup>(4)</sup> , SPI0_IO3			
VSS_4	27	Р		Default: VSS_4			
VDD_4	28	Р		Default: VDD_4			
PA4	29	VO		Default: PA4 Alternate2: SPI0_NSS, USART1_CK, DAC_OUT0, ADC01_IN4 Remap: SPI2_NSS, I2S2_WS			
PA5	30	VO		Default: PA5 Alternate2: SPI0_SCK, ADC01_IN5, DAC_OUT1			
PA 6	31	VO		Default: PA6 Alternate2: SPI0_MISO, TIMER7_BRKIN, ADC01_IN6, TIMER2_CH0, TIMER12_CH0 <sup>(4)</sup> Remap: TIMER0_BRKIN			
PA 7	32	VO		Default: PA7 Alternate2: SPI0_MOSI, TIMER7_CH0_ON, ADC01_IN7, TIMER2_CH1, TIMER13_CH0 <sup>(4)</sup> Remap: TIMER0_CH0_ON			
PC4	33	VO		Default: PC4 Alternate2: ADC01_IN14			
PC5	34	VO		Default: PC5 Alternate2: ADC01_IN15, WKUP4			
PB0	35	VO		Default: PB0 Alternate2: ADC01_IN8, TIMER2_CH2, TIMER7_CH1_ON Remap: TIMER0_CH1_ON			
PB1	36	VO		Default: PB1 Alternate1: SHRTIMER_SCOUT Alternate2: ADC01_IN9, TIMER2_CH3, TIMER7_CH2_ON Remap: TIMER0_CH2_ON			



	GD32E503Vx LQFP100							
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>				
PB2	37	VO	5VT	Default: PB2, BOOT1				
				Alternate1: SHRTIMER_SCIN				
DEZ	20	1/0	EV/T	Default: PE7				
PE7	38	VO	5VT	Alternate2: EXMC_D4 Remap: TIMER0_ETI				
				Default: PE8				
PE8	39	VO	5VT	Alternate2: EXMC D5				
1 20	00			Remap: TIMER0_CH0_ON				
				Default: PE9				
PE9	40	VO	5VT	Alternate2: EXMC_D6				
				Remap: TIMER0_CH0				
				Default: PE10				
PE10	41	VO	5VT	Alternate2: EXMC_D7				
				Remap: TIMER0_CH1_ON				
				Default: PE11				
PE11	42	VO	5VT	Alternate2: EXMC_D8				
				Remap: TIMER0_CH1				
		VO	5VT	Default: PE12				
PE12	43			Alternate2: EXMC_D9				
				Remap: TIMER0_CH2_ON				
		VO	5VT	Default: PE13				
PE13	44			Alternate2: EXMC_D10				
				Remap: TIMER0_CH2				
DE4.4	45	1/0	EV/T	Default: PE14				
PE14	45	I/O	5VT	Alternate2: EXMC_D11 Remap: TIMER0_CH3				
				Default: PE15				
PE15	46	46 VO	5VT	Alternate2: EXMC D12				
1210	10			Remap: TIMERO_BRKIN				
				Default: PB10				
				Alternate1: SHRTIMER_FLT2				
PB10	47	VO	5VT	Alternate2: I2C1_SCL, USART2_TX				
				Remap: TIMER1_CH2				
				Default: PB11				
DD44	40	1/0	EV/T	Alternate1: SHRTIMER_FLT3				
PBTT	PB11 48	VO	5VT	Alternate2: I2C1_SDA, USART2_RX				
				Remap: TIMER1_CH3				
VSS_1	49	Р		Default: VSS_1				
VDD_1	50	Р		Default: VDD_1				
				Default: PB12				
PB12	51	VO	5VT	Alternate1: SHRTIMER_ST2CH0				
1512			5V I	Alternate2: SPI1_NSS, I2S1_WS, I2C1_SMBA,				
				USART2_CK, TIMER0_BRKIN, CAN1_RX				
PB13	52	VO.	5VT	Default: PB13				



GD32E503Vx LQFP100						
B	F.	Pin	I/O	- (2)		
Pin Name	Pins	Type <sup>(1)</sup>	Level <sup>(2)</sup>	Functions description <sup>(3)</sup>		
				Alternate1: SHRTIMER_ST2CH1		
				Alternate2: SPI1_SCK, I2S1_CK, USART2_CTS,		
				TIMERO_CHO_ON, CAN1_TX, I2C1_TXFRAME		
				Default: PB14		
PB14	53	VO	5VT	Alternate1: SHRTIMER_ST3CH0, I2S1_ADD_SD		
1514	00			Alternate2: SPI1_MISO, USART2_RTS,		
				TIMER0_CH1_ON, TIMER11_CH0 <sup>(4)</sup>		
				Default: PB15		
PB15	54	VO	5VT	Alternate1: SHRTIMER_ST3CH1		
				Alternate2: SPI1_MOSI, TIMER0_CH2_ON,		
				I2S1_SD, TIMER11_CH1 <sup>(4)</sup> , WKUP6		
				Default: PD8		
PD8	55	VO	5VT	Alternate2: EXMC_D13		
				Remap: USART2_TX		
				Default: PD9		
PD9	56	VO	5VT	Alternate2: EXMC_D14		
				Remap: USART2_RX		
		VO	5VT	Default: PD10		
PD10	57			Alternate2: EXMC_D15		
				Remap: USART2_CK		
				Default: PD11		
PD11	58	VO	5VT	Alternate2: EXMC_A16/EXMC_CLE		
				Remap: USART2_CTS		
DD40	50	9 VO	5VT	Default: PD12		
PD12	59			Alternate2: EXMC_A17/EXMC_ALE		
				Remap: TIMER3_CH0, USART2_RTS		
DD40		1/0	5VT	Default: PD13		
PD13	60	VO		Alternate2: EXMC_A18		
				Remap: TIMER3_CH1		
DD4.4	61	VO	5\ /T	Default: PD14 Alternate2: EXMC_D0		
PD14	61	10	5VT			
				Remap: TIMER3_CH2 Default: PD15		
PD15	62	VO	5VT	Alternate2: EXMC_D1		
PDIS	02		301	Remap: TIMER3 CH3, CTC SYNC		
				Default: PC6		
				Alternate1: SHRTIMER_EXEV9, USART5_TX		
PC6	63	VO	5VT	Alternate2: I2S1_MCK, TIMER7_CH0, SDIO_D6		
				Remap: TIMER2_CH0		
		1		Default: PC7		
				Alternate1: SHRTIMER_FLT4, USART5_RX		
PC7	64	VO	5VT	Alternate2: I2S2_MCK, TIMER7_CH1, SDIO_D7		
				Remap: TIMER2_CH1		
	_			Default: PC8		
PC8	65	VO	5VT	Alternate1: SHRTIMER_ST4CH0, USART5_CK		



GD32E503Vx LQFP100				
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>
				Alternate2: TIMER7_CH2, SDIO_D0
				Remap: TIMER2_CH2 Default: PC9
PC9	66	VO	5VT	Alternate1: SHRTIMER_ST4CH1, I2C2_SDA Alternate2: TIMER7_CH3, SDIO_D1 Remap: TIMER2_CH3
PA8	67	VO	5VT	Default: PA8 Alternate1: SHRTIMER_ST0CH0, I2C2_SCL Alternate2: USART0_CK, TIMER0_CH0, CK_OUT, CTC_SYNC
PA9	68	VO	5VT	Default: PA9 Alternate1: SHRTIMER_ST0CH1, I2C2_SMBA Alternate2: USART0_TX, TIMER0_CH1
PA10	69	VO	5VT	Default: PA10 Alternate1: SHRTIMER_ST1CH0 Alternate2: USART0_RX, TIMER0_CH2
PA11	70	VO		Default: PA11 Alternate1: SHRTIMER_ST1CH1, USART5_TX Alternate2: USART0_CTS, CAN0_RX, USBDM, TIMER0_CH3
PA12	71	VO		Default: PA12 Alternate1: SHRTIMER_FLT0, USART5_RX Alternate2: USART0_RTS, CAN0_TX, USBDP, TIMER0_ETI
PA13	72	VO	5VT	Default: JTMS, SWDIO Remap: PA13
NC	73			-
VSS_2	74	Р		Default: VSS_2
VDD_2	75	Р		Default: VDD_2
PA 14	76	VO	5VT	Default: JTCK, SWCLK Remap: PA14
PA15	77	VO	5VT	Default: JTDI Alternate1: SHRTIMER_FLT1 Alternate2: SPI2_NSS, I2S2_WS Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
PC10	78	VO	5VT	Default: PC10 Alternate1: I2C2_SCL Alternate2: UART3_TX, SDIO_D2 Remap: USART2_TX, SPI2_SCK, I2S2_CK
PC11	79	VO	5VT	Default: PC11 Alternate1: SHRTIMER_EXEV1, I2S2_ADD_SD Alternate2: UART3_RX, SDIO_D3 Remap: USART2_RX, SPI2_MISO



	GD32E503Vx LQFP100				
	Pin I/O				
Pin Name	Pins	Type <sup>(1)</sup>	Level <sup>(2)</sup>	Functions description <sup>(3)</sup>	
				Default: PC12	
D040	90	1/0	EVT	Alternate1: SHRTIMER_EXEV0	
PC12	80	VO	5VT	Alternate2: UART4_TX, SDIO_CK	
				Remap: USART2_CK, SPI2_MOS1, I2S2_SD	
		VO	5VT	Default: PD0	
PD0	81			Alternate2: EXMC_D2	
				Remap: CAN0_RX	
		VO	5VT	Default: PD1	
PD1	82			Alternate2: EXMC_D3	
				Remap: CAN0_TX	
PD2	83	VO	5VT	Default: PD2	
. ==			3 / 1	Alternate2: TIMER2_ETI, UART4_RX, SDIO_CMD	
				Default: PD3	
PD3	84	VO	5VT	Alternate2: EXMC_CLK	
				Remap: USART1_CTS	
			5VT	Default: PD4	
PD4	85	VO		Alternate1: SHRTIMER_FLT2	
				Alternate2: EXMC_NOE	
				Remap: USART1_RTS	
		VO	5VT	Default: PD5	
PD5	86			Alternate1: SHRTIMER_EXEV2	
				Alternate2: EXMC_NWE	
				Remap: USART1_TX Default: PD6	
PD6	07	VO.	5VT	Alternate2: EXMC_NWAIT	
FDO	87			Remap: USART1_RX	
	88	VO	5VT	Default: PD7	
PD7				Alternate2: EXMC_NE0, EXMC_NCE1	
FDI				Remap: USART1_CK	
				Default: JTDO	
	89	VO	5VT	Alternate1: SHRTIMER_SCOUT,	
				SHRTIMER_EXEV8	
PB3				Alternate2: SPI2_SCK, I2S2_CK	
				Remap: TIMER1_CH1, PB3, SPI0_SCK,	
				TRACESWO	
	90	VO	5VT	Default: NJTRST	
PB4				Alternate1: SHRTIMER_EXEV6, l2C2_SDA,	
				I2S2_ADD_SD	
				Alternate2: SPI2_MISO, I2C0_TXFRAME	
				Remap: TIMER2_CH0, PB4, SPI0_MISO	
	91	VO		Default: PB5	
				Alternate1: SHRTIMER_EXEV5, I2C2_SCL	
PB5				Alternate2: I2C0_SMBA, SPI2_MOSI, I2S2_SD,	
				WKUP5	
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX	



	GD32E503Vx LQFP100				
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>	
PB6	92	VO	5VT	Default: PB6 Alternate1: SHRTIMER_SCIN, SHRTIMER_EXEV3 Alternate2: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2	
PB7	93	VO	5VT	Default: PB7 Alternate1: SHRTIMER_EXEV2 Alternate2: I2C0_SDA , TIMER3_CH1, EXMC_NA DV Remap: USART0_RX, SPI0_IO3	
воото	94	I		Default: BOOT0	
PB8	95	VO	5VT	Default: PB8 Alternate1: SHRTIMER_EXEV7, I2C2_SDA Alternate2: TIMER3_CH2, SDIO_D4, TIMER9_CH0 <sup>(4)</sup> Remap: I2C0_SCL, CAN0_RX	
PB9	96	VO	5VT	Default: PB9 Alternate1: SHRTIMER_EXEV4 Alternate2: TIMER3_CH3, SDIO_D5, TIMER10_CH0 <sup>(4)</sup> Remap: I2C0_SDA, CAN0_TX	
PE0	97	VO	5VT	Default: PE0 Alternate1: SHRTIMER_SCIN Alternate2: TIMER3_ETI, EXMC_NBL0	
PE1	98	VO	5VT	Default: PE1 Alternate1: SHRTIMER_SCOUT Alternate2: EXMC_NBL1	
VSS_3	99	Р		Default: VSS_3	
VDD_3	100	Р		Default: VDD_3	

#### Notes:

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Alternate1: The specified function can be mapped to the specific pin by configuring AFIO\_PCFA ~ AFIO\_PCFG registers.
  - Alternate2: These functions can be enabled with correct GPIO and function module mode configurations.
  - Remap: A group of the specified module functions can be mapped to the specified pins by configuring AFIO\_PCF0 ~ AFIO\_PCF1 registers.
- (4) Functions are available in GD32E503xE devices.



## 2.6.3. GD32E503Rx LQFP64 pin definitions

Table 2-5. GD32E503Rx LQFP64 pin definitions

	GD32E503RX LQFP64 pin definitions  GD32E503Rx LQFP64				
Pin Name	Pins	Pin (1)	I/O	Functions description <sup>(3)</sup>	
		Type <sup>(1)</sup>	Level <sup>(2)</sup>	D.C. II. M.DAT	
VBAT	1	Р		Default: VBAT	
PC13- TAMPER-	2	VO		Default: PC13 Alternate2: TAMPER-RTC, WKUP1	
RTC				Alternates. TAIVII ETCTO, WITOTT	
PC14-	3	VO		Default: PC14	
OSC32IN				Alternate2: OSC32IN	
PC15-	4	VO		Default: PC15	
OSC32OUT				Alternate2: OSC32OUT	
OSCIN	5	I		Default: OSCIN	
OSCOUT	6	0		Default: OSCOUT	
NRST	7	VO		Default: NRST	
PC0	8	<i>V</i> O		Default: PC0	
1 00		,,,		Alternate2: ADC012_IN10	
PC1	9	VO.		Default: PC1	
		, ,		Alternate2: ADC012_IN11	
				Default: PC2	
PC2	10	VO		Alternate1: I2S1_ADD_SD	
				Alternate2: ADC012_IN12	
PC3	11	VO		Default: PC3	
		_		Alternate2: ADC012_IN13	
VSSA	12	Р		Default: VSSA	
V DDA	13	Р		Default: VDDA	
		VO		Default: PA0	
PA0-WKUP	14			Alternate2: WKUP0, USART1_CTS, ADC012_IN0,	
				TIMER1_CH0, TIMER1_ETI, TIMER4_CH0,	
				TIMER7_ETI	
DA 4	15	VO		Default: PA1 Alternate2: USART1_RTS, ADC012_IN1,	
PA1				TIMER4_CH1, TIMER1_CH1	
		VO		Default: PA2	
PA2	16			Alternate2: USART1_TX, TIMER4_CH2, ADC012_IN2,	
FAZ				TIMER8_CH0 <sup>(4)</sup> , TIMER1_CH2, SPI0_IO2, WKUP3	
PA3		VO		Default: PA3	
	17			Alternate2: USART1_RX, TIMER4_CH3, ADC012_IN3,	
	• •			TIMER1_CH3, TIMER8_CH1 <sup>(4)</sup> , SPI0_IO3	
VSS_4	18	Р		Default: VSS 4	
VDD_4	19	Р		Default: VDD_4	
_	20	VO		Default: PA4	
PA4				Alternate2: SPI0_NSS, USART1_CK, DAC_OUT0,	
				ADC01_IN4	



GD32E503Rx LQFP64				
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>
				Remap: SPI2_NSS, I2S2_WS
PA5	21	VO		Default: PA5
				Alternate2: SPI0_SCK, ADC01_IN5, DAC_OUT1
				Default: PA6
PA6	22	VO		Alternate2: SPI0_MISO, TIMER7_BRKIN, ADC01_IN6,
				TIMER2_CH0, TIMER12_CH0 <sup>(4)</sup>
				Remap: TIMER0_BRKIN Default: PA7
				Alternate2: SPI0_MOSI, TIMER7_CH0_ON,
PA7	23	VO		ADC01_IN7, TIMER2_CH1, TIMER13_CH0 <sup>(4)</sup>
				Remap: TIMERO_CHO_ON
				Default: PC4
PC4	24	VO		Alternate2: ADC01_IN14
				Default: PC5
PC5	25	VO		Alternate2: ADC01_IN15, WKUP4
				Default: PB0
				Alternate2: ADC01_IN8, TIMER2_CH2,
PB0	26	VO		TIMER7_CH1_ON
				Remap: TIMER0_CH1_ON
				Default: PB1
				Alternate1: SHRTIMER_SCOUT
PB1	27	VO		Alternate2: ADC01_IN9, TIMER2_CH3,
				TIMER7_CH2_ON
				Remap: TIMER0_CH2_ON
PB2	28	VO	5VT	Default: PB2, BOOT1
				Alternate1: SHRTIMER_SCIN
		VO	5VT	Default: PB10
PB10	29			Alternate1: SHRTIMER_FLT2
				Alternate2: I2C1_SCL, USART2_TX
				Remap: TIMER1_CH2 Default: PB11
			5VT	Alternate1: SHRTIMER_FLT3
PB11	30	VO		Alternate2: I2C1_SDA, USART2_RX
				Remap: TIMER1_CH3
VSS_1	31	Р		Default: VSS_1
VDD_1	32	P		Default: VDD_1
, 55_1	02	<u> </u>		Default: PB12
PB12		VO	5\/T	Alternate1: SHRTIMER ST2CH0
	33			Alternate2: SP1_NSS, 12S1_WS, 12C1_SMBA,
				USART2_CK, TIMER0_BRKIN, CAN1_RX
	34	VO	5VT	Default: PB13
DD40				Alternate1: SHRTIMER_ST2CH1
PB13				Alternate2: SPI1_SCK, I2S1_CK, USART2_CTS,
				TIMER0_CH0_ON, CAN1_TX, I2C1_TXFRAME



GDJZLJUJXXDalaSNee							
			GD3	32E503Rx LQFP64			
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
PB14	35	VO	5VT	Default: PB14 Alternate1: SHRTIMER_ST3CH0, I2S1_ADD_SD Alternate2: SPI1_MISO, USART2_RTS, TIMER0_CH1_ON, TIMER11_CH0 <sup>(4)</sup>			
PB15	36	VO	5VT	Default: PB15 Alternate1: SHRTIMER_ST3CH1 Alternate2: SP1_MOSI, TIMER0_CH2_ON, I2S1_SD, TIMER11_CH1 <sup>(4)</sup> , WKUP6			
PC6	37	VO	5VT	Default: PC6 Alternate1: SHRTIMER_EXEV9, USART5_TX Alternate2: I2S1_MCK, TIMER7_CH0, SDIO_D6 Remap: TIMER2_CH0			
PC7	38	VO	5VT	Default: PC7 Alternate1: SHRTIMER_FLT4, USART5_RX Alternate2: I2S2_MCK, TIMER7_CH1, SDIO_D7 Remap: TIMER2_CH1			
PC8	39	VO	5VT	Default: PC8 Alternate1: SHRTIMER_ST4CH0USART5_CK			
PC9	40	VO	5VT	Default: PC9 Alternate1: SHRTIMER_ST4CH1, I2C2_SDA Alternate2: TIMER7_CH3, SDIO_D1 Remap: TIMER2_CH3			
PA8	41	VO	5VT	Default: PA8 Alternate1: SHRTIMER_ST0CH0, I2C2_SCL Alternate2: USART0_CK, TIMER0_CH0, CK_OUT, CTC_SYNC			
PA9	42	VO	5VT	Default: PA9 Alternate1: SHRTIMER_ST0CH1, I2C2_SMBA Alternate2: USART0_TX, TIMER0_CH1			
PA10	43	VO	5VT	Default: PA10 Alternate1: SHRTIMER_ST1CH0 Alternate2: USART0_RX, TIMER0_CH2			
PA11	44	VO		Default: PA11 Alternate1: SHRTIMER_ST1CH1, USART5_TX Alternate2: USART0_CTS, CAN0_RX, USBDM, TIMER0_CH3			
PA12	45	VO		Default: PA12 Alternate1: SHRTIMER_FLT0, USART5_RX Alternate2: USART0_RTS, CAN0_TX, USBDP, TIMER0_ETI			
PA13	46	VO	5VT	Default: JTMS, SWDIO Remap: PA13			
VSS_2	47	Р		Default: VSS_2			



			GD3	22E503Rx LQFP64
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>
VDD_2	48	Р		Default: VDD_2
D0.4.4	40	1/0	EV/T	Default: JTCK, SWCLK
PA14	49	VO	5VT	Remap: PA14
				Default: JTDI
PA15	50	VO	5VT	Alternate1: SHRTIMER_FLT1
17110	00	, ,	0 .	Alternate2: SPI2_NSS, I2S2_WS
				Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS
				Default: PC10
PC10	51	VO	5VT	Alternate1: I2C2_SCL
				Alternate2: UART3_TX, SDIO_D2
				Remap: USART2_TX, SPI2_SCK, I2S2_CK
				Default: PC11 Alternate1: SHRTIMER_EXEV1, I2S2_ADD_SD
PC11	52	VO	5VT	Alternate2: UART3 RX. SDIO D3
				Remap: USART2_RX, SPI2_MISO
				Default: PC12
				Alternate1: SHRTIMER EXEV0
PC12	53	VO	5VT	Alternate2: UART4 TX, SDIO CK
				Remap: USART2_CK, SPI2_MOSI, I2S2_SD
				Default: PD2
PD2	54	VO.	5VT	Alternate2: TIMER2_ETI, UART4_RX, SDIO_CMD
				Default: JTDO
DD2	EE	1/0	EV/T	Alternate1: SHRTIMER_SCOUT, SHRTIMER_EXEV8
PB3	55	VO	5VT	Alternate2: SPI2_SCK, I2S2_CK
				Remap: TIMER1_CH1, PB3, SPI0_SCK, TRACESWO
				Default: NJTRST
				Alternate1: SHRTIMER_EXEV6, I2C2_SDA,
PB4	56	VO	5VT	I2S2_ADD_SD
				Alternate2: SPI2_MISO, I2C0_TXFRAME
				Remap: TIMER2_CH0, PB4, SPI0_MISO
				Default: PB5
DDE	<b>57</b>	1/0		Alternate1: SHRTIMER_EXEV5, I2C2_SCL
PB5	57	VO		Alternate2: I2C0_SMBA, SPI2_MOSI, I2S2_SD, WKUP5
				Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX
				Default: PB6
				Alternate1: SHRTIMER_SCIN, SHRTIMER_EXEV3
PB6	58	VO	5VT	Alternate2: I2C0_SCL, TIMER3_CH0
				Remap: USART0_TX, CAN1_TX, SPI0_IO2
				Default: PB7
DD-7	<b>50</b>	1/0	E\ / <del>T</del>	Alternate1: SHRTIMER_EXEV2
PB7	59	VO	5VT	Alternate2: I2C0_SDA,TIMER3_CH1
				Remap: USART0_RX, SPI0_IO3
воото	60	1		Default: BOOT0



	GD32E503Rx LQFP64					
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>		
PB8	61	VO	5VT	Default: PB8 Alternate1: SHRTIMER_EXEV7, I2C2_SDA Alternate2: TIMER3_CH2, SDIO_D4, TIMER9_CH0 <sup>(4)</sup> Remap: I2C0_SCL, CAN0_RX		
PB9	62	VO	5VT	Default: PB9 Alternate1: SHRTIMER_EXEV4 Alternate2: TIMER3_CH3, SDIO_D5, TIMER10_CH0 <sup>(4)</sup> Remap: I2C0_SDA, CAN0_TX		
VSS_3	63	Р		Default: VSS_3		
VDD_3	64	Р		Default: VDD_3		

#### Notes:

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Alternate1: The specified function can be mapped to the specific pin by configuring AFIO\_PCFA ~ AFIO\_PCFG registers.

Alternate2: These functions can be enabled with correct GPIO and function module mode configurations.

Remap: A group of the specified module functions can be mapped to the specified pins by configuring AFIO\_PCF0 ~ AFIO\_PCF1 registers.

(4) Functions are available in GD32E503xE devices.



# 2.6.4. GD32E503Cx LQFP48 pin definitions

Table 2-6. GD32E503Cx LQFP48 pin definitions

			GD3	32E503Cx LQFP48			
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>			
VBAT	1	Р		Default: VBAT			
PC13- TAMPER- RTC	2	VO		Default: PC13 Alternate2: TAMPER-RTC, WKUP1			
PC14- OSC32IN	3	VO		Default: PC14 Alternate2: OSC32IN			
PC15- OSC32OUT	4	VO		Default: PC15 Alternate2: OSC32OUT			
OSCIN	5	I		Default: OSCIN			
OSCOUT	6	0		Default: OSCOUT			
NRST	7	VO		Default: NRST			
VSSA	8	Р		Default: VSSA			
V DDA	9	Р		Default: VDDA			
PA0-WKUP	10	VO		Default: PA0 Alternate2: WKUP0, USART1_CTS, ADC012_IN0, TIMER1_CH0, TIMER1_ETI, TIMER4_CH0			
PA1	11	VO		Default: PA1 Alternate2: USART1_RTS, ADC012_IN1, TIMER4_CH1, TIMER1_CH1			
PA2	12	VO		Default: PA2 Alternate2: USART1_TX, TIMER4_CH2, ADC012_IN2, TIMER8_CH0 <sup>(4)</sup> , TIMER1_CH2, SPI0_IO2, WKUP3			
PA3	13	VO		Default: PA3 Alternate2: USART1_RX, TIMER4_CH3, ADC012_IN3, TIMER1_CH3, TIMER8_CH1 <sup>(4)</sup> , SPI0_IO3			
PA4	14	VO		Default: PA4 Alternate2: SPI0_NSS, USART1_CK, DAC_OUT0, ADC01_IN4 Remap: SPI2_NSS, I2S2_WS			
PA5	15	VO		Default: PA5 Alternate2: SPI0_SCK, ADC01_IN5, DAC_OUT1			
PA6	16	VO		Default: PA6 Alternate2: SPI0_MISO, ADC01_IN6, TIMER2_CH0, TIMER12_CH0 <sup>(4)</sup> Remap: TIMER0_BRKIN			
PA7	17	VO		Default: PA7 Alternate2: SPI0_MOSI, ADC01_IN7, TIMER2_CH1, TIMER13_CH0 <sup>(4)</sup> Remap: TIMER0_CH0_ON			
PB0	18	VO.		Default: PB0			



			GD3	32E503Cx LQFP48
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>
				Alternate2: ADC01_IN8, TIMER2_CH2
				Remap: TIMER0_CH1_ON
				Default: PB1
PB1	19	VO		Alternate1: SHRTIMER_SCOUT
				Alternate2: ADC01_IN9, TIMER2_CH3
				Remap: TIMER0_CH2_ON
PB2	20	VO	5VT	Default: PB2, BOOT1
				Alternate1: SHRTIMER_SCIN
				Default: PB10
PB10	21	VO	5VT	Alternate1: SHRTIMER_FLT2
				Alternate2: I2C1_SCL, USART2_TX Remap: TIMER1_CH2
				Default: PB11
				Alternate1: SHRTIMER FLT3
PB11	22	VO	5VT	Alternate2: I2C1_SDA, USART2_RX
				Remap: TIMER1_CH3
VSS_1	23	Р		Default: VSS 1
VDD_1	24	P		Default: VDD_1
V DD_1	24			Default: PB12
				Alternate1: SHRTIMER_ST2CH0
PB12	25	VO	5VT	Alternate2: SPI1_NSS, I2S1_WS, I2C1_SMBA,
				USART2_CK, TIMER0_BRKIN, CAN1_RX
				Default: PB13
				Alternate1: SHRTIMER ST2CH1
PB13	26	VO	5VT	Alternate2: SPI1_SCK, I2S1_CK, USART2_CTS,
				TIMERO_CHO_ON, CAN1_TX, I2C1_TXFRAME
				Default: PB14
DD4.4	07	1/0	5) /T	Alternate1: SHRTIMER_ST3CH0, I2S1_ADD_SD
PB14	27	VO	5VT	Alternate2: SPI1_MISO, USART2_RTS,
				TIMER0_CH1_ON, TIMER11_CH0 <sup>(4)</sup>
				Default: PB15
PB15	28	VO	5VT	Alternate1: SHRTIMER_ST3CH1
1010	20	"	3 1	Alternate2: SPI1_MOSI, TIMER0_CH2_ON, I2S1_SD,
				TIMER11_CH1 <sup>(4)</sup> , WKUP6
				Default: PA8
PA8	29	VO	5VT	Alternate1: SHRTIMER_ST0 CH0, I2C2_SCL
17.0	20		3 7 1	Alternate2: USART0_CK, TIMER0_CH0, CK_OUT,
				CTC_SYNC
				Default: PA9
PA9	30	VO	5VT	Alternate1: SHRTIMER_ST0CH1, I2C2_SMBA
				Alternate2: USART0_TX, TIMER0_CH1
	_			Default: PA10
PA10	31	VO	5VT	Alternate1: SHRTIMER_ST1CH0
				Alternate2: USART0_RX, TIMER0_CH2



			GD3	32E503Cx LQFP48		
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>		
PA11	32	VO		Default: PA11 Alternate1: SHRTIMER_ST1CH1 Alternate2: USART0_CTS, CAN0_RX, USBDM, TIMER0_CH3		
PA12	33	VO		Default: PA12 Alternate1: SHRTIMER_FLT0 Alternate2: USART0_RTS, CAN0_TX, USBDP, TIMER0 ETI		
PA13	34	VO	5VT	Default: JTMS, SWDIO Remap: PA13		
VSS_2	35	Р		Default: VSS_2		
VDD_2	36	Р		Default: VDD_2		
PA14	37	VO	5VT	Default: JTCK, SWCLK Remap: PA14		
PA15	38	VO	5VT	Default: JTDI Alternate1: SHRTIMER_FLT1 Alternate2: SPI2_NSS, I2S2_WS Remap: TIMER1_CH0, TIMER1_ETI, PA15, SPI0_NSS		
PB3	39	VO	5VT	Default: JTDO Alternate1: SHRTIMER_SCOUT, SHRTIMER_EXEV8 Alternate2: SPI2_SCK, I2S2_CK Remap: TIMER1_CH1, PB3, SPI0_SCK, TRACESWO		
PB4	40	VO	5VT	Default: NJTRST Alternate1: SHRTIMER_EXEV6, I2C2_SDA, I2S2_ADD_SD Alternate2: SPI2_MISO, I2C0_TXFRAME Remap: TIMER2_CH0, PB4, SPI0_MISO		
PB5	41	VO		Default: PB5 Alternate1: SHRTIMER_EXEV5, I2C2_SCL Alternate2: I2C0_SMBA, SPI2_MOSI, I2S2_SD, WKUP5 Remap: TIMER2_CH1, SPI0_MOSI, CAN1_RX		
PB6	42	VO	5VT	Default: PB6 Alternate1: SHRTIMER_SCIN, SHRTIMER_EXEV3 Alternate2: I2C0_SCL, TIMER3_CH0 Remap: USART0_TX, CAN1_TX, SPI0_IO2		
PB7	43	VO	5VT	Default: PB7 Alternate1: SHRTIMER_EXEV2 Alternate2: I2C0_SDA, TIMER3_CH1 Remap: USART0_RX, SPI0_IO3		
BOOT0	44	I		Default: BOOT0		
PB8	45	VO	5VT	Default: PB8 Alternate1: SHRTIMER_EXEV7, I2C2_SDA Alternate2: TIMER3_CH2, TIMER9_CH0 <sup>(4)</sup>		



	GD32E503Cx LQFP48				
Pin Name	Pins	Pin Type <sup>(1)</sup>	I/O Level <sup>(2)</sup>	Functions description <sup>(3)</sup>	
				Remap: I2C0_SCL, CAN0_RX	
PB9	46	VO	5VT	Default: PB9 Alternate1: SHRTIMER_EXEV4 Alternate2: TIMER3_CH3, TIMER10_CH0 <sup>(4)</sup> Remap: I2C0_SDA, CAN0_TX	
VSS_3	47	Р		Default: VSS_3	
VDD_3	48	Р		Default: VDD_3	

#### Notes:

- (1) Type: I = input, O = output, P = power.
- (2) I/O Level: 5VT = 5 V tolerant.
- (3) Alternate1: The specified function can be mapped to the specific pin by configuring AFIO\_PCFA ~ AFIO\_PCFG registers.

Alternate2: These functions can be enabled with correct GPIO and function module mode configurations.

Remap: A group of the specified module functions can be mapped to the specified pins by configuring AFIO\_PCF0 ~ AFIO\_PCF1 registers.

(4) Functions are available in GD32E503xE devices.



# 3. Functional description

#### 3.1. Arm<sup>®</sup> Cortex<sup>®</sup>-M33 core

The Cortex®-M33 processor is a 32-bit processor that possesses low interrupt latency and low-cost debug. The characteristics of integrated and advanced make the Cortex®-M33 processor suitable for market products that require microcontrollers with high performance and low power consumption.

32-bit Arm® Cortex®-M33 processor core

- Up to 180 MHz operation frequency
- Ultra-low power, energy-efficient operation
- Integrated Nested Vectored Interrupt Controller (NVIC)
- 24-bit SysTick timer

The Cortex®-M33 processor is based on the ARMv8 architecture and supports both Thumb and Thumb-2 instruction sets. Some system peripherals listed below are also provided by Cortex®-M33:

- Internal Bus Matrix connected with Code bus, System bus, and Private Peripheral Bus (PPB) and debug accesses
- Nested Vectored Interrupt Controller (NVIC)
- Breakpoint Unit (BPU)
- Data Watchpoint and Trace (DWT)
- Instrumentation Trace Macrocell (ITM)
- Serial Wire JTAG Debug Port (SWJ-DP)
- Trace Port Interface Unit (TPIU)
- Memory Protection Unit (MPU)
- Floating Point Unit (FPU)
- DSP Extension (DSP)

# 3.2. Embedded memory

- Up to 512 Kbytes of Flash memory
- Up to 128 Kbytes of SRAM with hardware parity checking

512 Kbytes of inner Flash and 128 Kbytes of inner SRAM at most is available for storing programs and data, and Flash is accessed (Read) at CPU clock speed with 0~4 waiting time. *Table 2-2. GD32E503xx memory map* shows the memory map of the GD32E503xx series of devices, including code, SRAM, peripheral, and other pre-defined regions.



## 3.3. Clock, reset and supply management

- Internal 8 MHz factory-trimmed RC and external 4 to 32 MHz crystal oscillator
- Internal 48 MHz RC oscillator
- Internal 40 KHz RC calibrated oscillator and external 32.768 KHz crystal oscillator
- Integrated system clock PLL
- 1.71 to 3.63 V application supply and I/Os
- Supply Supervisor: POR (Power On Reset), PDR (Power Down Reset), and low voltage detector (LVD)

The Clock Control Unit (CCU) provides a range of oscillator and clock functions. These include speed internal RC oscillator and external crystal oscillator, high speed and low speed two types. Several prescalers allow the frequency configuration of the AHB and two APB domains. The maximum frequency of the AHB, APB2 and APB1 domains is 180 MHz/180 MHz/90 MHz. See *Figure 2-6. GD32E503xx clock tree* for details on the clock tree.

The Reset Control Unit (RCU) controls three kinds of reset: system reset resets the processor core and peripheral IP components. Power-on reset (POR) and power-down reset (PDR) are always active, and ensures proper operation starting from 1.56 V and down to 1.52V. The device remains in reset mode when  $V_{DD}$  is below a specified threshold. The embedded low voltage detector (LVD) monitors the power supply, compares it to the voltage threshold and generates an interrupt as a warning message for leading the MCU into security.

Power supply schemes:

- V<sub>DD</sub> range: 1.71 to 3.63 V, external power supply for I/Os and the internal regulator. Provided externally through V<sub>DD</sub> pins.
- V<sub>SSA</sub>, V<sub>DDA</sub> range: 1.71 to 3.63 V, external analog power supplies for ADC, reset blocks, RCs and PLL.
- V<sub>BAK</sub> range: 1.71 to 3.63 V, power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V<sub>DD</sub> is not present.

#### 3.4. Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from main Flash memory (default)
- Boot from system memory
- Boot from on-chip SRAM

In default condition, boot from main Flash memory is selected. The boot loader is located in the internal boot ROM memory (system memory). It is used to reprogram the Flash memory by using USART0 (PA9 and PA10) or USART1 (PD5 and PD6).



## 3.5. Power saving modes

The MCU supports five kinds of power saving modes to achieve even lower power consumption. They are Sleep, Deep-sleep, Deep-sleep 1, Deep-sleep 2 and Standby mode. These operating modes reduce the power consumption and allow the application to achieve the best balance between the CPU operating time, speed and power consumption.

#### ■ Sleep mode

In sleep mode, only the clock of CPU core is off. All peripherals continue to operate and any interrupt/event can wake up the system.

#### ■ **Deep-sleep** mode

In Deep-sleep mode, all clocks in the 1.1V domain are off, and all of IRC8M, IRC48M, HXTAL and PLLs are disabled. The contents of SRAM and registers are preserved. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep mode including the 16 external lines, the RTC alarm, LVD output, USB wakeup, I2C2 wakeup and USART5 wakeup. When exiting the deep-sleep mode, the IRC8M is selected as the system clock.

#### ■ Deep-sleep 1 mode

In Deep-sleep 1 mode, all clocks in the 1.1V domain are off, and all of IRC8M, IRC48M, HXTAL and PLLs are disabled. The power of COREOFF1 domain is cut off. The contents of registers in COREOFF1 domain are lost. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep 1 mode including the 16 external lines, the RTC alarm, LVD output, USB wakeup, I2C2 wakeup and USART5 wakeup. Waking up from Deep-sleep 1 mode needs an additional delay to power on COREOFF1 domain. When exiting the deep-sleep 1 mode, the IRC8M is selected as the system clock.

#### ■ Deep-sleep 2 mode

In Deep-sleep 2 mode, all clocks in the 1.1V domain are off, and all of IRC8M, IRC48M, HXTAL and PLLs are disabled. The power of COREOFF0/COREOFF1 domain is cut off. The contents of SRAM except for the first 32K and registers in COREOFF0/COREOFF1 domain are lost. Any interrupt or wakeup event from EXTI lines can wake up the system from the deep-sleep mode including the 16 external lines, the RTC alarm, LVD output, USB wakeup, I2C2 wakeup and USART5 wakeup. Waking up from Deep-sleep 2 mode needs an additional delay to power on COREOFF1 domain. Waking up from Deep-sleep 2 mode needs an additional delay to power on COREOFF0/COREOFF1 domain. When exiting the deep-sleep 2 mode, the IRC8M is selected as the system clock.

#### ■ Standby mode

In Standby mode, the whole 1.1V domain is power off, the LDO is shut down, and all of IRC8M, IRC48M, HXTAL and PLL are disabled. There are four wakeup sources for the Standby mode, including the external reset from NRST pin, the RTC alarm, the FWDGT reset, and the rising edge on WKUP pins.



## 3.6. Analog to digital converter (ADC)

- 12-bit SAR ADC's conversion rate is up to 2.5 MSPS
- 12-bit, 10-bit, 8-bit or 6-bit configurable resolution
- Hardware oversampling ratio adjustable from 2 to 256x improves resolution to 16-bit
- Input voltage range: V<sub>REF-</sub> to V<sub>REF+</sub>
- Temperature sensor

Three 12-bit 2.5 MSPS multi-channel ADCs are integrated in the device. It has a total of 18 multiplexed channels: up to 16 external channels, 1 channel for internal temperature sensor ( $V_{\text{SENSE}}$ ) and 1 channel for internal reference voltage ( $V_{\text{REFINT}}$ ). The input voltage range is between  $V_{\text{REF-}}$  and  $V_{\text{REF+}}$ . An on-chip hardware oversampling scheme improves performance while off-loading the related computational burden from the CPU. The analog watchdog allows the application to detect whether the input voltage goes outside the user-defined higher or lower thresholds. A configurable channel management block can be used to perform conversions in single, continuous, scan or discontinuous mode to support more advanced use.

The ADC can be triggered from the events generated by the general level 0 timers (TIMERx), the advanced timers (TIMER0 and TIMER7) and SHRTIMER with internal connection. The temperature sensor can be used to generate a voltage that varies linearly with temperature. It is internally connected to the ADC\_IN16 input channel which is used to convert the sensor output voltage in a digital value.

To ensure a high accuracy on ADC and DAC, the ADC/DAC independent external reference voltage should be connected to  $V_{REF+}/V_{REF-}$  pins. According to the different packages,  $V_{REF+}$  pin can be connected to  $V_{DDA}$  pin, or external reference voltage,  $V_{REF-}$  pin must be connected to  $V_{SSA}$  pin. The  $V_{REF+}$  pin is only available on no less than 100-pin packages, or else the  $V_{REF-}$  pin is not available and internally connected to  $V_{DDA}$ . The  $V_{REF-}$  pin is only available on no less than 100-pin packages, or else the  $V_{REF-}$  pin is not available and internally connected to  $V_{SSA}$ .

# 3.7. Digital to analog converter (DAC)

- Two 12-bit DACs with independent output channels
- 8-bit or 12-bit mode in conjunction with the DMA controller

The 12-bit buffered DAC is used to generate variable analog outputs. The DAC channels can be triggered by the timer, SHRTIMER or EXTI with DMA support. In dual DAC channel operation, conversions could be done independently or simultaneously. The maximum output value of the DAC is  $V_{\text{REF+}}$ .

#### 3.8. DMA

7 channels for DMA0 controller and 5 channels for DMA1 controller



 Peripherals supported: Timers, SHRTIMER, SDIO, ADCs, DACs, SPIs, I2Cs, USARTs and I2S

The flexible general-purpose DMA controllers provide a hardware method of transferring data between peripherals and/or memory without intervention from the CPU, thereby freeing up bandwidth for other system functions. Three types of access method are supported: peripheral to memory, memory to peripheral, memory to memory.

Each channel is connected to fixed hardware DMA requests. The priorities of DMA channel requests are determined by software configuration and hardware channel number. Transfer size of source and destination are independent and configurable.

## 3.9. General-purpose inputs/outputs (GPIOs)

- Up to 112 fast GPIOs, all mappable on 16 external interrupt lines
- Analog input/output configurable
- Alternate function input/output configurable

There are up to 112 general purpose I/O pins (GPIO) in GD32E503xx, named PA0  $\sim$  PA15, PB0  $\sim$  PB15, PC0  $\sim$  PC15, PD0  $\sim$  PD15, PE0  $\sim$  PE15, PF0  $\sim$  PF15 and PG0  $\sim$  PG15 to implement logic input/output functions. Each of the GPIO ports has related control and configuration registers to satisfy the requirements of specific applications. The external interrupts on the GPIO pins of the device have related control and configuration registers in the Interrupt/event controller (EXTI). The GPIO ports are pin-shared with other alternative functions (AFs) to obtain maximum flexibility on the package pins. Each of the GPIO pins can be configured by software as output (push-pull or open-drain), input, peripheral alternate function or analog mode. Most of the GPIO pins are shared with digital or analog alternate functions.

# 3.10. Timers and PWM generation

- Two 16-bit advanced timer (TIMER0, TIMER7), one 32-bit general timer (TIMER1), up to nine 16-bit general timers (TIMER2 ~ TIMER4, TIMER8 ~ TIMER13), and two 16-bit basic timer (TIMER5, TIMER6)
- Up to 4 independent channels of PWM, output compare or input capture for each general timer and external trigger input
- 16-bit, motor control PWM advanced timer with programmable dead-time generation for output match
- Encoder interface controller with two inputs using quadrature decoder
- 24-bit SysTick timer down counter
- 2 watchdog timers (free watchdog timer and window watchdog timer)

The advanced timer (TIMER0, TIMER7) can be used as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable dead-time generation. It



can also be used as a complete general timer. The 4 independent channels can be used for input capture, output compare, PWM generation (edge- or center- aligned counting modes) and single pulse mode output. If configured as a general 16-bit timer, it has the same functions as the TIMERx timer. It can be synchronized with external signals or to interconnect with other general timers together which have the same architecture and features.

The general timer can be used for a variety of purposes including general time, input signal pulse width measurement or output waveform generation such as a single pulse generation or PWM output, up to 4 independent channels for input capture/output compare. TIMER1 is based on a 32-bit auto-reload up/down counter and a 16-bit prescaler. TIMER2 ~ TIMER4 is based on a 16-bit auto-reload up/down counter and a 16-bit prescaler. TIMER8 ~ TIMER13 is based on a 16-bit auto-reload up counter and a 16-bit prescaler. The general timer also supports an encoder interface with two inputs using quadrature decoder.

The basic timer, known as TIMER5 &TIMER6, are mainly used for DAC trigger generation. They can also be used as a simple 16-bit time base.

The GD32E503xx have two watchdog peripherals, free watchdog timer and window watchdog timer. They offer a combination of high safety level, flexibility of use and timing accuracy.

The free watchdog timer includes a 12-bit down-counting counter and an 8-stage prescaler. It is clocked from an independent 40 KHz internal RC and as it operates independently of the main clock, it can operate in deep-sleep, deep-sleep 1, deep-sleep 2 and standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management.

The window watchdog timer is based on a 7-bit down counter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early wakeup interrupt capability and the counter can be frozen in debug mode.

The SysTick timer is dedicated for OS, but could also be used as a standard down counter. The features are shown below:

- A 24-bit down counter
- Auto reload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

# 3.11. Real time clock (RTC)

- 32-bit programmable counter with a programmable 20-bit prescaler
- Alarm function
- Interrupt and wakeup event

The real time clock is an independent timer which provides a set of continuously running counters in backup registers to provide a real calendar function, and provides an alarm interrupt or an expected interrupt. The RTC features a 32-bit programmable counter for long-



term measurement using the compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 KHz from external crystal oscillator.

## 3.12. Inter-integrated circuit (I2C)

#### I2C0 and I2C1:

- Support both master and slave mode with a frequency up to 1 MHz (Fast mode plus)
- Provide arbitration function, optional PEC (packet error checking) generation and checking
- Supports 7-bit and 10-bit addressing mode and general call addressing mode
- SMBus 2.0 and PMBus compatible
- Supports SAM V mode

#### 12C2:

- Support both master and slave mode with a frequency up to 1 MHz (Fast mode plus)
- Provide arbitration function, optional PEC (packet error checking) generation and checking
- Supports 7-bit and 10-bit addressing mode and general call addressing mode
- SMBus 3.0 and PMBus 1.3 compatible
- Wakeup from Deep-sleep mode on address match

The I2C interface is an internal circuit allowing communication with an external I2C interface which is an industry standard two line serial interface used for connection to external hardware. These two serial lines are known as a serial data line (SDA) and a serial clock line (SCL). The I2C module provides different data transfer rates: up to 100 KHz in standard mode, up to 400 KHz in the fast mode and up to 1 MHz in the fast mode plus. The I2C module also has an arbitration detect function to prevent the situation where more than one master attempts to transmit data to the I2C bus at the same time. A CRC-8 calculator is also provided in I2C interface to perform packet error checking for I2C data.

# 3.13. Serial peripheral interface (SPI)

- Up to three SPI interfaces with a frequency of up to 22.5 MHz
- Support both master and slave mode
- Hardware CRC calculation and transmit automatic CRC error checking
- Quad-SPI configuration available in master mode (only in SPI0)

The SPI interface uses 4 pins, among which are the serial data input and output lines (MISO & MOSI), the clock line (SCK) and the slave select line (NSS). All SPIs can be served by the DMA controller. The SPI interface may be used for a variety of purposes, including simplex synchronous transfers on two lines with a possible bidirectional data line or reliable communication using CRC checking. Quad-SPI master mode is also supported in SPIO.



# 3.14. Universal synchronous asynchronous receiver transmitter (USART)

#### USART0~2, UART3~4:

- Maximum speed up to 22.5 MBits/s
- Supports both asynchronous and clocked synchronous serial communication modes
- IrDA SIR encoder and decoder support
- LIN break generation and detection
- ISO 7816-3 compliant smart card interface

#### **USART5**:

- Maximum speed up to 22.5 MBits/s
- Supports both asynchronous and clocked synchronous serial communication modes
- IrDA SIR encoder and decoder support
- LIN break generation and detection
- ISO 7816-3 compliant smart card interface
- Dual clock domain
- Wake up from Deep-sleep mode

The USART (USART0, USART1, USART2, USART5) are used to translate data between parallel and serial interfaces, provides a flexible full duplex data exchange using synchronous or asynchronous transfer. It is also commonly used for RS-232 standard communication. The USART includes a programmable baud rate generator which is capable of dividing the system clock to produce a dedicated clock for the USART transmitter and receiver. The USART also supports DMA function for high speed data communication.

# 3.15. Inter-IC sound (I2S)

- Two I2S bus Interfaces with sampling frequency from 8 KHz to 192 KHz
- Support either master or slave mode

The Inter-IC sound (I2S) bus provides a standard communication interface for digital audio applications by 4-wire serial lines. GD32E503xx contain an I2S-bus interface that can be operated with 16/32 bit resolution in master or slave mode, pin multiplexed with SPI1 and SPI2. The audio sampling frequency from 8 KHz to 192 KHz is supported.

# 3.16. Universal Serial Bus full-speed device interface (USBD)

- USB 2.0 full-speed device controller.
- Support USB 2.0 Link Power Management.
- Shared dedicated 512-byte SRAM used for data packet buffer with CAN.
- Integrated USB PHY.



The Universal Serial Bus full-speed device interface (USBD) module contains a full-speed internal USB PHY and no more external PHY chip is needed. USBD supports all the four types of transfer (control, bulk, interrupt and isochronous) defined in USB 2.0 protocol. USBD supports 8 USB endpoints that can be individually configured.

## 3.17. Controller area network (CAN)

■ Two CAN interfaces supports the CAN protocols version 2.0A and B, ISO11891-1:2015 specification with baud rates up to 1 Mbit/s when classical frames.

Controller area network (CAN) is a method for enabling serial communication in field bus. The CAN protocol has been used extensively in industrial automation and automotive applications. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three mailboxes for transmission and two FIFOs of three messages depth for reception. The CANO and CAN1 provides 28 scalable/configurable identifier filter banks for selecting the incoming messages needed and discarding the others.

## 3.18. External memory controller (EXMC)

- Supported external memory: SRAM, PSRAM, ROM and NOR-Flash, NAND Flash and PC card
- Up to 16-bit data bus
- Support to interface with Motorola 6800 and Intel 8080 type LCD directly

External memory controller (EXMC) is an abbreviation of external memory controller. It is divided in to several sub-banks for external device support, each sub-bank has its own chip selection signal but at one time, only one bank can be accessed. The EXMC support code execution from external memory except NAND Flash and PC card. The EXMC also can be configured to interface with the most common LCD module of Motorola 6800 and Intel 8080 series and reduce the system cost and complexity.

# 3.19. Secure digital input/output interface (SDIO)

■ Support SD2.0/SDIO2.0/MMC4.2/CE-ATA1.1 host and device interface

The Secure Digital Input and Output Card Interface (SDIO) provides access to external SD memory cards specifications version 2.0, SDIO card specification version 2.0, multi-media card system specification version 4.2 and CE-ATA digital protocol version 1.1 with DMA supported.

# 3.20. Super High-Resolution Timer (SHRTIMER)

■ High- precision timing units: Master\_TIMER, Slave\_TIMERx (x=0..4).



- Synchronization outputs: synchronize external resources as master.
- Synchronization inputs: be synchronized as a slaver.
- Bunch mode controller to handle light-load operation.
- 6 DMA request: Master\_TIMER requests, Slave\_TIMERx (x=0..4) requests.

SHRTIMER has a high-precision counting clock and can be used for high-precision timing. It can generate 10 high precision and flexible digital signals to control motor or be used for power management applications. It has multiple internal signals connected to the ADC and DAC. It can be used for control and monitoring purposes. It can handle various fault input for safe purposes.

## 3.21. Serial/Quad Parallel Interface (SQPI)

- SQPI controller support configuring output clock frequency which is divided by HCLK.
- SQPI controller support no address phase and data phase operation which is named special command by the controller.
- SQPI controller support 256MB external memory space.

  Logic memory address range: 0xB000\_0000 0xBFFF\_FFF.
- SQPI controller support 6 types mode for different combination of command, address, waitcycle, and data phase.

Serial/Quad Parallel Interface (SQPI) is a controller for external serial/dual/quad parallel interface memory peripheral. For example: SQPI-PSRAM and SQPI-FLASH. With this controller, users can use external SQPI interface memory as SRAM simply.

# 3.22. Debug mode

■ Serial wire JTAG debug port (SWJ-DP)

The Arm® SWJ-DP Interface is embedded and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

# 3.23. Package and operation temperature

- LQFP144 (GD32E503Zx), LQFP100 (GD32E503Vx), LQFP64 (GD32E503Rx) and LQFP48 (GD32E503Cx).
- Operation temperature range: -40°C to +105°C for grade 7 devices.
- Operation temperature range: -40°C to +85°C for grade 6 devices.



## 4. Electrical characteristics

## 4.1. Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 4-1. Absolute maximum ratings<sup>(1)(4)</sup>

Symbol	Parameter	Min	Max	Unit
$V_{DD}$	External voltage range <sup>(2)</sup>	V <sub>SS</sub> - 0.3	V <sub>SS</sub> + 3.63	V
$V_{DDA}$	External analog supply voltage	V <sub>SSA</sub> - 0.3	V <sub>SSA</sub> + 3.63	V
V <sub>BAT</sub>	External battery supply voltage	V <sub>SS</sub> - 0.3	V <sub>SS</sub> + 3.63	V
V <sub>IN</sub>	Input voltage on 5V tolerant pin <sup>(3)</sup>	V <sub>SS</sub> - 0.3	V <sub>DD</sub> + 3.63	V
V IN	Input voltage on other I/O	V <sub>SS</sub> - 0.3	3.63	V
ΔV <sub>DDx</sub>	Variations between different VDD power pins		50	mV
V <sub>SSX</sub> -V <sub>SS</sub>	Variations between different ground pins		50	mV
lio	Maximum current for GPIO pins		±25	mA
T <sub>A</sub>	Operating temperature range	-40	+85	°C
	Pow er dissipation at T <sub>A</sub> = 85°C of LQFP144 <sup>(5)</sup>	_	820	
	Pow er dissipation at T <sub>A</sub> = 85°C of LQFP100 <sup>(5)</sup>	_	813	
P <sub>D</sub>	Pow er dissipation at T <sub>A</sub> = 85°C of LQFP64 <sup>(5)</sup>	_	733	mW
	Pow er dissipation at T <sub>A</sub> = 85°C of LQFP48 <sup>(5)</sup>	_	574	
	Pow er dissipation at T <sub>A</sub> = 105°C of LQFP48 <sup>(5)</sup>	_	287	
T <sub>STG</sub>	Storage temperature range	-65	+150	°C
$T_J$	Maximum junction temperature	_	125	°C

<sup>(1)</sup> Guaranteed by design, not tested in production.

# 4.2. Operating conditions characteristics

Table 4-2. DC operating conditions

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
$V_{DD}$	Supply voltage		1.71	3.3	3.63	V
\/·	Analog supply voltage, f <sub>ADCMAX</sub> = 35 MHz		2.4	3.3	3.63	V
$V_{DDA}$	Analog supply voltage, f <sub>ADCMAX</sub> = 14 MHz		1.71	_	3.63	V
$V_{BAT}$	Battery supply voltage		1.71 <sup>(2)</sup>	_	3.63	V

<sup>(1)</sup> Based on characterization, not tested in production.

<sup>(2)</sup> All main power and ground pins should be connected to an external power source within the allowable range.

<sup>(3)</sup> V<sub>IN</sub> maximum value cannot exceed 5.5 V.

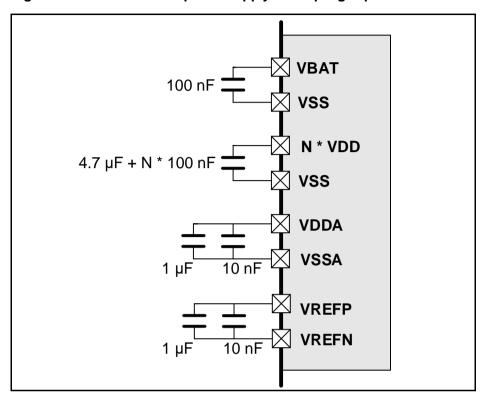
<sup>(4)</sup> It is recommended that  $V_{DD}$  and  $V_{DDA}$  are powered by the same source. The maximum difference between  $V_{DD}$  and  $V_{DDA}$  does not exceed 300 mV during power-up and operation.

<sup>(5)</sup> For grade 6 devices, the parameter of  $T_A=85^{\circ}C$ , For grade 7 devices, the parameter of  $T_A=105^{\circ}C$ .



(2) In the application which V<sub>BAT</sub> supply the backup domains, if the VBAT voltage drops below the minimum value, when V<sub>DD</sub> is powered on again, it is necessary to refresh the registers of backup domains and enable LXTAL again.

Figure 4-1. Recommended power supply decoupling capacitors (1)(2)



- (1) The VREFP and VREFN pins are only available on no less than 100-pin packages, or else the VREFP and VREFN pins are not available and internally connected to VDDA and VSSA pins.
- (2) All decoupling capacitors need to be as close as possible to the pins on the PCB board.

Table 4-3. Clock frequency(1)

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>HCLK</sub>	AHB clock frequency		1	180	MHz
f <sub>APB1</sub>	APB1 clock frequency			90	MHz
f <sub>APB2</sub>	APB2 clock frequency			180	MHz

(1) Guaranteed by design, not tested in production.

Table 4-4. Operating conditions at Power up/ Power down<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
	V <sub>DD</sub> rise time rate		0	8	/\/
t <sub>VDD</sub>	V <sub>DD</sub> fall time rate	_	50	∞	µs/ V

(1) Guaranteed by design, not tested in production.

Table 4-5. Start-up timings of Operating conditions<sup>(1)(2)(3)</sup>

		0		
Symbol	Parameter	Conditions	Тур	Unit
t <sub>start-up</sub>	Start up time	Clock source from HXTAL	608	
	Start-up time	Clock source from IRC8M	74	μs

<sup>(1)</sup> Based on characterization, not tested in production.

<sup>(2)</sup> After power-up, the start-up time is the time between the rising edge of NRST high and the first I/O instruction conversion in SystemInitfunction.



(3) PLL is off.

Table 4-6. Power saving mode wakeup timings characteristics(1)(2)

Symbol	Parameter	Тур	Unit
t <sub>Sleep</sub>	Wakeup from Sleep mode	1.7	
	Wakeup from Deep-sleep mode (LDO On)	3.1	
	Wakeup from Deep-sleep mode (LDO in low power mode)	3.1	
<sub>to</sub> .	Wakeup from Deep-sleep mode1 (LDO in low power and low	4.2	
tDeep-sleep	driver mode)	4.3	μs
	Wakeup from Deep-sleep mode2 (LDO in low power and low	11.7	
	driver mode)	11.7	
t <sub>Standby</sub>	Wakeup from Standby mode	77.2	

<sup>(1)</sup> Based on characterization, not tested in production.

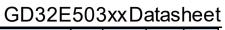
# 4.3. Power consumption

The power measurements specified in the tables represent that code with data executing from on-chip Flash with the following specifications.

Table 4-7. Power consumption characteristics (2)(3)(4)(5)(6)

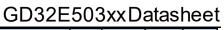
Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 180 MHz, All peripherals enabled		59.8		mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 180 MHz, All peripherals disabled		26.1		mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 160 MHz, All peripherals enabled		53.6		mA
l <sub>DD</sub> +l <sub>DDA</sub>	Supply current (Run mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 160 MHz, All peripherals disabled		23.5	1	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 120 MHz, All peripherals enabled		41	ı	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 120 MHz, All peripherals disabled		18.2	١	mA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$ System clock = 108 MHz, All peripherals enabled	_	37.2	_	mA

<sup>(2)</sup> The wakeup time is measured from the wakeup event to the point at which the application code reads the first instruction under the below conditions:  $V_{DD} = V_{DDA} = 3.3 \text{ V}$ , IRC8M = System clock= 8 MHz.



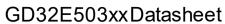


Curre le - I	Douglas of a m	Conditions Min Typ(1) May I				
Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 108 MHz, All peripherals	_	16.6	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 96 MHz, All peripherals	_	33.4	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 96 MHz, All peripherals	_	15	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 72 MHz, All peripherals	_	25.7	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 72 MHz, All peripherals	_	11.8	_	mΑ
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 48 MHz, All peripherals	_	18	_	mΑ
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 48 MHz, All peripherals	_	7.96	_	mΑ
		disabled				
		V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz,				
		System clock = 36 MHz, All peripherals	_	14	_	mΑ
		enabled				
		V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz,				
		System clock = 36 MHz, All peripherals	l _	6.49	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 24 MHz, All peripherals		9.73		mΑ
		enabled		0.70		
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 24 MHz, All peripherals		4.83		mΑ
		disabled		4.00		111/5
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$		7.0		A
		System clock = 16 MHz, All peripherals		7.2	_	mA
		enabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$		0.0		A
		System clock = 16 MHz, All peripherals	_	3.9	-	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, \text{HXTAL} = 25 \text{ MHz},$				
		System clock = 8 MHz, All peripherals	-	4.62	_	mA
		enabled				



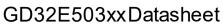


Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System clock = 8 MHz, All peripherals	_	2.9	_	mA
		disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 180 MHz, CPU clock off,	_	47.8	_	mΑ
		All peripherals enabled				
		V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 180 MHz, CPU clock off,	_	9.5	_	mA
		All peripherals disabled				
		V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 160 MHz, CPU clock off,	_	42.8	_	mA
		All peripherals enabled				
		V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz,				
		System Clock = 160 MHz, CPU clock off,	_	8.7	_	mΑ
		All peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 120 MHz, CPU clock off,		32.8	_	mA
		All peripherals enabled		02.0		
	$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$					
		System Clock = 120 MHz, CPU clock off,		7.07		mA
		All peripherals disabled		7.07		
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
	Supply current	System Clock = 108 MHz, CPU clock off,	_	29.8		mA
	(Sleep mode)	All peripherals enabled		20.0		110
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 108 MHz, CPU clock off,	_	6.57		mA
		All peripherals disabled		0.07		
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 96 MHz, CPU clock off, All	_	26.7	_	mΑ
		peripherals enabled		20.7		117
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 96 MHz, CPU clock off, All	_	6.1		mA
		peripherals disabled		0.1		110
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
		System Clock = 72 MHz, CPU clock off, All		20.7		mA
				20.7		111/-
	peripherals enabled					
		V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz, System Clock = 72 MHz CPU clock off All	_	5.1		mA
		System Clock = 72 MHz, CPU clock off, All		J. I		111/-1
		peripherals disabled				
		$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$		11 =		<b>س</b> ۸
		System Clock = 48 MHz, CPU clock off, All	_	14.5	_	mA
		peripherals enabled				





Ţ	Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
ł	Cy	i ai aiii otoi	$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$		. , ,	шах	- Cint
			System Clock = 48 MHz, CPU clock off, All	_	4.1	_	mΑ
			peripherals disabled		7.1		1101
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			, , , , , , , , , , , , , , , , , , ,		11.4		mΛ
			System Clock = 36 MHz, CPU clock off, All		11.4		mA
			peripherals enabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			System Clock = 36 MHz, CPU clock off, All	_	3.6	_	mA
			peripherals disabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			System Clock = 24 MHz, CPU clock off, All	_	8.3	_	mA
			peripherals enabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			System Clock = 24 MHz, CPU clock off, All	_	3.1	_	mΑ
			peripherals disabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			System Clock = 16 MHz, CPU clock off, All	_	6.2	_	mΑ
			peripherals enabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			System Clock = 16 MHz, CPU clock off, All	_	2.7	_	mΑ
			peripherals disabled				
			V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, HXTAL = 25 MHz,				
			System Clock = 8 MHz, CPU clock off, All	_	4.2		mΑ
			peripherals enabled				
			$V_{DD} = V_{DDA} = 3.3 \text{ V, HXTAL} = 25 \text{ MHz,}$				
			System Clock = 8 MHz, CPU clock off, All		2.4		mA
			peripherals disabled		2.7		111/5
			V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V, LDO in normal power				
			•		404.00		
			and normal driver mode, IRC40K off, RTC off	_	461.33		μA
		Supply current	$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in low power and}$	_	413.00	_	μΑ
		(Deep-Sleep	normal driver mode, IRC40K off, RTC off				
		mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in normal power}$	_	258.00	_	μA
			and low driver mode, IRC40K off, RTC off				·
			$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO}$ in low power and	_	210.67	_	μA
			low driver mode, IRC40K off, RTC off				
		Supply current	$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in low power and}$				
		(Deep-Sleep 1	low driver mode, IRC40K off, RTC off		163.33	_	μΑ
		mode)	ion divertibue, increase off, isto off				
		Supply current	$V_{DD} = V_{DDA} = 3.3 \text{ V, LDO in low power and}$				
		(Deep-Sleep 2	low driver mode, IRC40K off, RTC off	—	68.00	_	μΑ
		mode)	low driver flode, inchor off, NTC off				





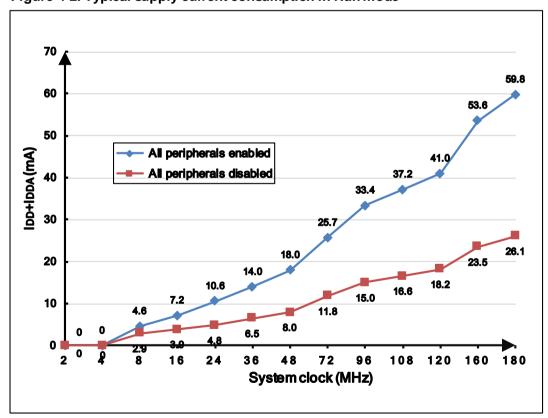
Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
Зушьог	Parameter		IVIIII	тур	IVIAX	Unit
		$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K on,}$ RTC on	_	3.79		μA
	Supply current (Standby mode)	$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K}$ on, RTC off		3.58		μA
		$V_{DD} = V_{DDA} = 3.3 \text{ V, LXTAL off, IRC40K off,}$ RTC off	_	3.08	_	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 3.63 V, LXTAL on with external crystal, RTC on, LXTAL High driving		1.95		μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL High driving		1.82	ı	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL High driving		1.67	ı	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 1.8 V, LXTAL on with external crystal, RTC on, LXTAL High driving	_	1.59	_	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 3.63 $V$ , LXTAL on with external crystal, RTC on, LXTAL Medium High driving	1	1.53	ı	μΑ
Іват	Battery supply current (Backup	$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving		1.40		μΑ
	mode)	$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving	_	1.25	_	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 1.8 V, LXTAL on with external crystal, RTC on, LXTAL Medium High driving		1.18	ı	μΑ
		V <sub>DD</sub> off, V <sub>DDA</sub> off, V <sub>BAT</sub> = 3.63 V, LXTAL on w ith external crystal, RTC on, LXTAL Medium Low driving		1.12	ı	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 3.3 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving		0.99		μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT}$ = 2.5 V, LXTAL on with external crystal, RTC on, LXTAL Medium Low driving	_	0.84	_	μΑ
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT} = 1.8 \text{ V}$ , LXTAL on with external crystal, RTC on, LXTAL	_	0.77	—	μΑ



0200						
Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
		Medium Low driving				
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT} = 3.63 \text{ V}$ , LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	1.00	_	μΑ
		driving				
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT} = 3.3 \text{ V}$ , LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	0.87	_	μΑ
		driving				
		V <sub>DD</sub> off, V <sub>DDA</sub> off, V <sub>BAT</sub> = 2.5 V, LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	0.72	_	μΑ
		driving				
		$V_{DD}$ off, $V_{DDA}$ off, $V_{BAT} = 1.8 \text{ V}$ , LXTAL on				
		with external crystal, RTC on, LXTAL Low	_	0.64	_	μΑ
		driving				

- (1) Based on characterization, not tested in production.
- (2) Unless otherwise specified, all values given for  $T_A = 25$  °C and test result is mean value.
- (3) When System Clockis less than 4 MHz, an external source is used, and the HXTAL bypass function is needed, no PLL.
- (4) When System Clock is greater than 8 MHz, a crystal 8 MHz is used, and the HXTAL bypass function is closed, using PLL.
- (5) When analog peripheral blocks such as ADCs, DACs, HXTAL, LXTAL, IRC8M, or IRC40K are ON, an additional power consumption should be considered.
- (6) All GPIOs are configured as an alog mode except standby mode.

Figure 4-2. Typical supply current consumption in Run mode





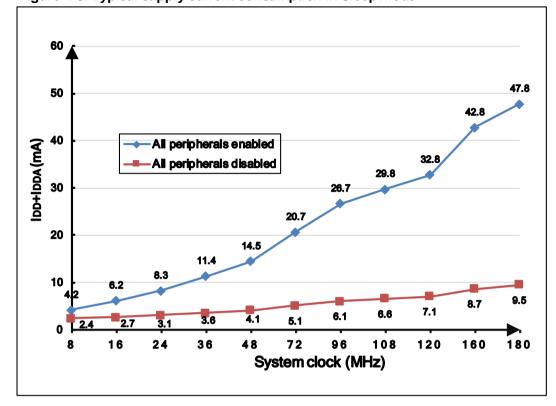


Figure 4-3. Typical supply current consumption in Sleep mode

#### 4.4. EMC characteristics

EMS (electromagnetic susceptibility) includes ESD (Electrostatic discharge, positive and negative) and FTB (Burst of Fast Transient voltage, positive and negative) testing result is given in <u>Table 4-8. EMS characteristics</u>(1), based on the EMS levels and classes compliant with IEC 61000 series standard.

Table 4-8. EMS characteristics(1)

Valtage applied to all device pipe to	$V_{DD} = 3.3 \text{ V},$	
Voltage applied to all device pins to induce a functional disturbance	LQFP144, f <sub>HCLK</sub> = 180 MHz conforms to IEC 61000-4-2	3A
Fast transient voltage burst applied to	V <sub>DD</sub> = 3.3 V, LQFP144, f <sub>HCLK</sub> = 180 MHz	4A
	0 11	st transient voltage burst applied to $V_{DD} = 3.3 \text{ V}$ , uce a functional disturbance through LQFP144, $f_{HCLK} = 180 \text{ MHz}$

<sup>(1)</sup> Based on characterization, not tested in production.

EMI (Electromagnetic Interference) emission test result is given in the <u>Table 4-9. EMI</u> <u>characteristics</u>(1), The electromagnetic field emitted by the device are monitored while an application, executing EEMBC code, is running. The test is compliant with SAE J1752-3:2017 standard which specifies the test board and the pin loading.



Table 4-9. EMI characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Tested frequency band	Max vs. [f <sub>HXTAL</sub> /f <sub>HCLK</sub> ] 8/180 MHz	Unit
		$V_{DD} = 3.6 \text{ V}, T_A = +23 ^{\circ}\text{C},$	0.15 MHz to 30 MHz	-7.58	
Sемі	Peak level	LQFP144, f <sub>HCLK</sub> = 180	30 MHz to 130 MHz	3.35	dΒμV
OLIVII		MHz, conforms to SAE	420 MILE to 4 OLE	4.05	
		J1752-3:2017	130 MHz to 1 GHz	4.25	

<sup>(1)</sup> Based on characterization, not tested in production.

# 4.5. Power supply supervisor characteristics

Table 4-10. Power supply supervisor characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		LVDT<2:0> = 000(rising edge)	_	2.19		
		LVDT<2:0> = 000(falling edge)		2.08		
		LVDT<2:0> = 001(rising edge)	ı	2.33		
		LVDT<2:0> = 001(falling edge)	_	2.22	_	
		LVDT<2:0> = 010(rising edge)		2.48	_	
		LVDT<2:0> = 010(falling edge)		2.36		
		LVDT<2:0> = 011(rising edge)	_	2.62	_	
V <sub>LVD</sub> <sup>(1)</sup>	Low voltage	LVDT<2:0> = 011(falling edge)	_	2.51	_	V
V LVD( · )	Detector level selection	LVDT<2:0> = 100(rising edge)		2.75		V
		LVDT<2:0> = 100(falling edge)	_	2.65	_	
		LVDT<2:0> = 101(rising edge)		2.9	_	
		LVDT<2:0> = 101(falling edge)		2.79		
		LVDT<2:0> = 110(rising edge)		3.04		
		LVDT<2:0> = 110(falling edge)		2.93		
		LVDT<2:0> = 111(rising edge)		3.19		
		LVDT<2:0> = 111(falling edge)		3.07	_	
V <sub>LVDhyst</sub> (2)	LVD hysteresis	_	_	100	_	mV
V <sub>POR</sub> <sup>(1)</sup>	Power on reset threshold	_		1.56		V
V <sub>PDR</sub> <sup>(1)</sup>	Pow er down reset threshold	_	—	1.52	_	V



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>PDRhyst</sub> <sup>(2)</sup>	PDR hysteresis		l	40		mV
V <sub>BOR3</sub> <sup>(2)</sup>	Brow nout level 3 threshold	Falling edge	1	2.8	-	٧
	Blow flout level 3 tillesfloid	Rising edge	I	2.9		V
V <sub>BOR2</sub> (2)	Brow nout level 2 threshold	Falling edge		2.5	_	V
V BOR2\	Brow flout level 2 tiffesfloid	Rising edge	I	2.6		V
V <sub>BOR1</sub> (2)	Brow nout level 1 threshold	Falling edge	_	2.2	_	V
V BOR1 <sup>(-)</sup>	Brow hout level 1 threshold	Rising edge		2.3		V
V <sub>BORhyst</sub> <sup>(2)</sup>	BOR hysteresis	_		100	_	mV
t <sub>RSTTEMPO</sub> (2)	Reset temporization	_	_	2.88	-	ms

<sup>(1)</sup> Based on characterization, not tested in production.

## 4.6. Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample. Static latch-up (LU) test is based on the two measurement methods.

Table 4-11. ESD characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V=05 (UDI II)	Electrostatic discharge ESDA/JEDEC JS-001-		6000		V	
VESD(HBM)	voltage (human body model)	2017		0000		V
V <sub>ESD(CDM)</sub>	Electrostatic discharge	ESDA/JEDEC JS-002-		1000		V
	voltage (charge device model)	2018		1000		V

<sup>(1)</sup> Based on characterization, not tested in production.

Table 4-12. Static latch-up characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
111	- I-test	JESD78E		200		mA
LU	V <sub>supply</sub> over voltage		_	5.4	_	V

<sup>(1)</sup> Based on characterization, not tested in production.

#### 4.7. External clock characteristics

Table 4-13. High speed external clock (HXTAL) generated from a crystal/ceramic

<sup>(2)</sup> Guaranteed by design, not tested in production.



#### characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HXTAL</sub> (1)	Crystal or ceramic frequency	$1.71 \text{ V} \le \text{V}_{DD} \le 3.63 \text{ V}$	4	8	32	MHz
R <sub>F</sub> <sup>(2)</sup>	Feedback resistor	V <sub>DD</sub> = 3.3 V	_	400	_	kΩ
C <sub>HXTAL</sub> (2)(3)	Recommended load capacitance on OSCIN and OSCOUT	_	_	20	30	pF
Ducy <sub>(HXTAL)</sub> <sup>(2)</sup>	Crystal or ceramic duty cycle		30	50	70	%
g <sub>m</sub> (2)	Oscillator transconductance	Startup	_	25	_	mA/V
IDDHXTAL <sup>(1)</sup>	Crystal or ceramic operating current	$V_{DD} = 3.3 \text{ V, } f_{HCLK} =$ $f_{IRC8M} = 8 \text{ MHz}$	_	0.42	_	mA
tsuhxtal <sup>(1)</sup>	Crystal or ceramic startup time	$V_{DD} = 3.3 \text{ V, } f_{HCLK} =$ $f_{IRC8M} = 8 \text{ MHz}$	_	2	_	ms

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.
- (3)  $C_{HXTAL1} = C_{HXTAL2} = 2*(C_{LOAD} C_S)$ , For  $C_{HXTAL1}$  and  $C_{HXTAL2}$ , it is recommended matching capacitance on OSCIN and OSCOUT. For  $C_{LOAD}$ , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer For  $C_S$ , it is PCB and MCU pin stray capacitance.

Table 4-14. High speed external clock characteristics (HXTAL in bypass mode)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HXTAL_ext</sub> <sup>(1)</sup>	External clock source or	1.71 V ≤ V <sub>DD</sub> ≤	1		F0	MHz
	oscillator frequency	3.63 V	I	1	50	IVI⊓∠
V <sub>HXTALH</sub> <sup>(2)</sup>	OSCIN input pin high level voltage		0.7 V <sub>DD</sub>	_	$V_{DD}$	٧
V <sub>HXTALL</sub> <sup>(2)</sup>	OSCIN input pin low level	$V_{DD} = 3.3 \text{ V}$	Vss		0.3 V <sub>DD</sub>	V
V HXTALL\	voltage		VSS		0.5 VDD	٧
t <sub>H/L(HXTAL)</sub> (2)	OSCIN high or low time	_	5		_	ns
t <sub>R/F(HXTAL)</sub> (2)	OSCIN rise or fall time	_	_	_	10	ns
C <sub>IN</sub> <sup>(2)</sup>	OSCIN input capacitance	_	_	5	_	pF
Ducy <sub>(HXTAL)</sub> <sup>(2)</sup>	Duty cycle	<u> </u>	40	_	60	%

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.

Table 4-15. Low speed external clock (LXTAL) generated from a crystal/ceramic



#### characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LXTAL</sub> <sup>(1)</sup>	Crystal or ceramic frequency	V <sub>DD</sub> = 3.3 V	_	32.768	_	kHz
C <sub>LXTAL</sub> <sup>(2)(3)</sup>	Recommended matching capacitance on OSC32IN and OSC32OUT	I	l	10		pF
Ducy <sub>(LXTAL)</sub> <sup>(2)</sup>	Crystal or ceramic duty cycle		30	_	70	%
		Low er driving capability		4		
gm <sup>(2)</sup>	Oscillator transconductance	Medium low driving capability	ĺ	6	1	µA/V
ym∵ ∕	Oscillator transconductance	Medium high driving capability		12		μΑ/ν
		Higher driving capability	ı	18		
		LXTALDRI[1:0] = 00		0.7		
I <sub>DDLXTAL</sub> (1)	Crystal or ceramic operating	LXTALDRI[1:0] = 01	_	0.8	_	μA
IDDLX IAL'	current	LXTALDRI[1:0] = 10		1.2		μΛ
		LXTALDRI[1:0] = 11		1.6	_	
tsulxtal <sup>(1)(4)</sup>	Crystal or ceramic startup	-	_	2	_	S

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.
- (3)  $C_{LXTAL1} = C_{LXTAL2} = 2*(C_{LOAD} C_S)$ , For  $C_{LXTAL1}$  and  $C_{LXTAL2}$ , it is recommended matching capacitance on SC32IN and OSC32OUT. For  $C_{LOAD}$ , it is crystal/ceramic load capacitance, provided by the crystal or ceramic manufacturer. For  $C_S$ , it is PCB and MCU pin stray capacitance.
- (4) t<sub>SULXTAL</sub> is the startup time measured from the moment it is enabled (by software) to the 32.768 kHz oscillator stabilization flags is SET. This value varies significantly with the crystal manufacturer.

Table 4-16. Low speed external user clock characteristics (LXTAL in bypass mode)

Table 1 for Lott operational about the articles (Lixtuic in by passing at								
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
£ (1)	External clock source or	.,		00.700	4000	1.11		
f <sub>LXTAL_ext</sub> <sup>(1)</sup>	oscillator frequency	V <sub>DD</sub> = 3.3 V		32.768	1000	kHz		
V <sub>LXTALH</sub> <sup>(2)</sup>	OSC32IN input pin high level		0.7 V <sub>DD</sub>		V			
V LXTALH\' /	voltage		U.7 VDD	_	$V_{DD}$	V		
V (2)	OSC32IN input pin low level		Vss		0.3 V <sub>DD</sub>	V		
V <sub>LXTALL</sub> <sup>(2)</sup>	voltage		VSS		0.3 V DD			
$t_{H/L(LXTAL)}^{(2)}$	OSC32IN high or low time	_	450	_	_			
$t_{R/F(LXTAL)}^{(2)}$	OSC32IN rise or fall time		_	1	50	ns		
C <sub>IN</sub> <sup>(2)</sup>	OSC32IN input capacitance	_	_	5	_	pF		
Ducy <sub>(LXTAL)</sub> (2)	Duty cycle	_	30	50	70	%		

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.



## 4.8. Internal clock characteristics

Table 4-17. High speed internal clock (IRC8M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>IRC8M</sub>	High Speed Internal Oscillator (IRC8M) frequency	V <sub>DD</sub> = V <sub>DDA</sub> = 3.3 V		8		MHz
A CC <sub>IRC8M</sub>	IDCOM and illator Francisco	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C} \text{ for grade}$ 6 devices		-0.862 to 0.887 <sup>(1)</sup>		%
	IRC8M oscillator Frequency - accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 \text{ °C } \sim +105 \text{ °C for}$ grade 7 devices	_	-1.55 to 0.887 <sup>(1)</sup>	_	%
		$V_{DD} = V_{DDA} = 3.3 \text{ V}, T_A = 25 ^{\circ}\text{C}$	-1.0	_	+1.0	%
	IRC8M oscillator Frequency accuracy, User trimming step <sup>(1)</sup>	_	ı	0.5	l	%
Ducy <sub>IRC8M</sub> <sup>(2)</sup>	IRC8M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	45	50	55	%
IDDAIRC8M <sup>(1)</sup>	IRC8M oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V},$	_	80		μΑ
tsuirc8m <sup>(1)</sup>	IRC8M oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V},$	_	1.5	_	μs

<sup>(1)</sup> Based on characterization, not tested in production.

Table 4-18. Low speed internal clock (IRC40K) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>IRC40K</sub> <sup>(1)</sup>	Low Speed Internal oscillator	$V_{DD} = V_{DDA} = 3.3 \text{ V},$	20	40	45	kHz
	(IRC40K) frequency	$T_A = -40 ^{\circ}\text{C} \sim +85 ^{\circ}\text{C}$	20	40		KHZ
(2)	IRC40K oscillator operating	$V_{DD} = V_{DDA} = 3.3 \text{ V},$		0.4	_	
IDDAIRC40K <sup>(2)</sup>	current	f <sub>HCLK</sub> = f <sub>HXTAL_PLL</sub> = 180 MHz	_	0.4		μA
tsuirc40K <sup>(2)</sup>	IRC40K oscillator startup	$V_{DD} = V_{DDA} = 3.3 \text{ V},$		00		
	time	f <sub>HCLK</sub> = f <sub>HXTAL_PLL</sub> = 180 MHz		80		μs

 $<sup>(1) \</sup>quad \hbox{Guaranteed by design, not tested in production.}$ 

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(2)</sup> Based on characterization, not tested in production.



Table 4-19. High speed internal clock (IRC48M) characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>IRC48M</sub>	High Speed Internal Oscillator (IRC48M) frequency	V <sub>DD</sub> = 3.3 V	_	48	_	MHz
ACCirc48M	IDC49M conillator Fraguesia	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 ^{\circ}\text{C} ^{\circ}\text{+85} ^{\circ}\text{C for}$ grade 6 devices		-2.013 to 1.023 <sup>(1)</sup>	_	%
	IRC48M oscillator Frequency - accuracy, Factory-trimmed	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $T_A = -40 ^{\circ}\text{C} \sim +105 ^{\circ}\text{C} \text{ for}$ grade 7 devices		-2.871 to 1.023 <sup>(1)</sup>	_	%
		$V_{DD} = V_{DDA} = 3.3 \text{ V}$	-2.0		+2.0	%
	IRC48M oscillator Frequency accuracy, User trimming step <sup>(1)</sup>	-•		0.12	_	%
D <sub>IRC48M</sub> <sup>(2)</sup>	IRC48M oscillator duty cycle	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	45	50	55	%
IDDAIRC48M <sup>(1)</sup>	IRC48M oscillator operating current	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL\_PLL} = 180 \text{ MHz}$	_	286.9	_	μΑ
tsuirc48M <sup>(1)</sup>	IRC48M oscillator startup time	$V_{DD} = V_{DDA} = 3.3 \text{ V},$ $f_{HCLK} = f_{HXTAL\_PLL} = 180 \text{ MHz}$	_	3.68	_	μs

<sup>(1)</sup> Based on characterization, not tested in production.

## 4.9. PLL characteristics

Table 4-20. PLL characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PLLIN</sub> <sup>(1)</sup>	PLL input clock frequency		2		16	MHz
f <sub>PLLOUT</sub> <sup>(2)</sup>	PLL output clock frequency	_	16	_	180	MHz
f <sub>VCO</sub> <sup>(2)</sup>	PLL VCO output clock	_	32		360	MHz
TVCO	frequency				300	IVII IZ
t <sub>LOCK</sub> (2)	PLL lock time	_	_	_	300	μs
I <sub>DDA</sub> <sup>(1)(3)</sup>	Current consumption on $V_{DDA}$	VCO freq = 360 MHz	_	700	_	μΑ
$I_{DD}^{(1)(3)}$	Current consumption on $V_{\text{DD}}$	VCO freq = 360 MHz	_	500	_	μΑ
	Cycle to cycle Jitter			40		
Jitter <sub>PLL</sub> <sup>(1)(4)</sup>	(rms)	System clock	40		ne	
Jitterpll(1)(4)	Cycle to cycle Jitter			400		ps
	(peak to peak)			400		

<sup>(1)</sup> Based on characterization, not tested in production.

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(3)</sup> System clock = IRC8M = 8 MHz, PLL clocksource = IRC8M/2 = 4 MHz,  $f_{PLLOUT}$  = 180 MHz.

 $<sup>(4) \</sup>quad \text{Value given with main PLL running}. \\$ 



Table 4-21. PLL1 characteristics

Table 1 2111 221 offaractoriolise									
Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
f <sub>PLLIN</sub> <sup>(1)</sup>	PLL input clock frequency	_	2	_	16	MHz			
f <sub>PLLOUT</sub> <sup>(2)</sup>	PLL output clock frequency	_	16	_	100	MHz			
f <sub>VCO</sub> <sup>(2)</sup>	PLL VCO output clock frequency	Ι	32	_	180	MHz			
t <sub>LOCK</sub> (2)	PLL lock time	_	_	_	300	μs			
I <sub>DDA</sub> <sup>(1)</sup>	Current consumption on V <sub>DDA</sub>	VCO freq = 180 MHz	_	400	_	μA			
I <sub>DD</sub> <sup>(1)</sup>	Current consumption on V <sub>DD</sub>	VCO freq = 180 MHz	_	250	_	μA			
Jitter <sub>PLL</sub> (1)	Cycle to cycle Jitter		_	40	_	ps			

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.

Table 4-22. PLL2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PLLIN</sub> <sup>(1)</sup>	PLL input clock frequency		2	_	16	MHz
f <sub>PLLOUT</sub> <sup>(2)</sup>	PLL output clock frequency		16	_	200	MHz
f <sub>VCO</sub> <sup>(2)</sup>	PLL VCO output clock frequency	-	32	_	360	MHz
t <sub>LOCK</sub> (2)	PLL lock time		_	_	300	μs
I <sub>DDA</sub> <sup>(1)</sup>	Current consumption on V <sub>DDA</sub>	VCO freq = 360 MHz	_	700	_	μΑ
I <sub>DD</sub> <sup>(1)</sup>	Current consumption on V <sub>DD</sub>	VCO freq = 360 MHz	_	500	_	μA
Jitter <sub>PLL</sub> (1)	Cycle to cycle Jitter	_	_	40		ps

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.

Table 4-23. PLLUSB characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PLLIN</sub> <sup>(1)</sup>	PLL input clock frequency		4	_	30	MHz
f <sub>PLLOUT</sub> <sup>(2)</sup>	PLL output clock frequency			480		MHz
t <sub>LOCK</sub> (2)	PLL lock time	_	_	100	150	μs
Jitter <sub>PLL</sub> <sup>(1)</sup>	Cycle to cycle Jitter	_		40	_	ps

- $(1) \quad \text{Based on characterization, not tested in production.}$
- (2) Guaranteed by design, not tested in production.

Table 4-24. PLL spread spectrum clock generation (SSCG) characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>mod</sub>	Modulation frequency	_		_	10	KHz
mdamp	Peak modulation amplitude	_	_	_	2	%
MODCNT*					2 <sup>15</sup> -1	
MODSTEP	_	_	_	_	2''-1	_

<sup>(1)</sup> Guaranteed by design, not tested in production.

#### **Equation 1**: SSCG configuration equation:

 $MODCNT = round(f_{PLLIN}/4/f_{mod})$ 

MODSTEP = round(mdamp\*PLLN\*2<sup>15</sup>/(MODCNT\*100))

The formula above (*Equation 1*) is SSCG configuration equation.



# 4.10. Memory characteristics

Table 4-25. Flash memory characteristics

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Typ <sup>(1)</sup>	Max	Unit
	Number of guaranteed					
PECYC	program /erase cycles	_	10	_	_	kcycles
	before failure (Endurance)					
t <sub>RET</sub>	Data retention time	_	10	_	_	years
t <sub>PROG</sub>	Word programming time		_	37.5	_	μs
terase	Page erase time	T <sub>A</sub> range <sup>(2)</sup>	_	11	_	ms
t <sub>MERASE</sub>	Mass erase time		_	12	_	S

<sup>(1)</sup> Based on characterization, not tested in production.

# 4.11. NRST pin characteristics

Table 4-26. NRST pin characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST Input low level voltage			-	$0.35\ V_{DD}$	V
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST Input high level voltage	$V_{DD} = V_{DDA} = 1.71 \text{ V}$	0.65 V <sub>DD</sub>	ı		V
V <sub>hyst</sub> <sup>(1)</sup>	Schmidt trigger Voltage hysteresis			120	1	mV
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST Input low level voltage			1	$0.35\ V_{DD}$	V
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST Input high level voltage	$V_{DD} = V_{DDA} = 3.3 \text{ V}$	0.65 V <sub>DD</sub>		_	V
V <sub>hyst</sub> <sup>(1)</sup>	Schmidt trigger Voltage hysteresis		_	180	_	mV
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST Input low level voltage		_	_	$0.35\ V_{DD}$	V
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST Input high level voltage	$V_{DD} = V_{DDA} = 3.63 \text{ V}$	0.65 V <sub>DD</sub>	_		V
V <sub>hyst</sub> <sup>(1)</sup>	Schmidt trigger Voltage hysteresis		_	200		mV
R <sub>pu</sub> <sup>(2)</sup>	Pull-up equivalent resistor	_	_	40	_	kΩ

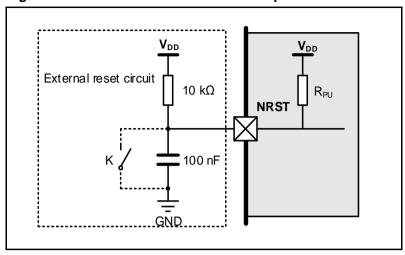
<sup>(1)</sup> Based on characterization, not tested in production.

<sup>(2)</sup> For grade 6 devices,  $T_A$  range= -40°  $C \sim +85$ °C. For grade 7 devices,  $T_A$  range= -40°  $C \sim +105$ °C.

 $<sup>(2) \</sup>quad \text{Guaranteed by design, not tested in production.}$ 



Figure 4-4. Recommended external NRST pin circuit<sup>(1)</sup>



 $(1) \qquad \text{Unless the voltage on NRST pingo below $V_{\text{IL(NRST)}}$ level, the device would not generate a reliable reset.}$ 



## 4.12. **GPIO** characteristics

Table 4-27. I/O port DC characteristics(1)(3)

Symbol	Paramet	er	Conditions	Min	Тур	Max	Unit
V	Standard IO Low level input voltage		1.71 V $\leq$ V <sub>DD</sub> = V <sub>DDA</sub> $\leq$ 3.63 V	_	_	0.35 V <sub>DD</sub>	V
V <sub>IL</sub>	5V-tolerant IO Low level input voltage		1.71 V ≤ V <sub>DD</sub> = V <sub>DDA</sub> ≤ 3.63 V	_	_	0.35 V <sub>DD</sub>	V
V	Standard IO Low voltage	•	1.71 V $\leq$ V <sub>DD</sub> = V <sub>DDA</sub> $\leq$ 3.63 V	0.65 V <sub>DD</sub>	_	_	V
V <sub>IH</sub>	5V-tolerant IO L input volta		1.71 V $\leq$ V <sub>DD</sub> = V <sub>DDA</sub> $\leq$ 3.63 V	0.65 V <sub>DD</sub>	_	_	V
	Low level outpu	t voltage	V <sub>DD</sub> = 1.71V		_	0.19	
$V_{OL}$	for an 10 Pin		V <sub>DD</sub> = 3.3 V	_	_	0.12	V
	$(I_{10} = +8 \text{ mA})$		V <sub>DD</sub> = 3.63V		_	0.11	
	Low level outpu	t voltage	V <sub>DD</sub> = 1.71V		_	0.61	
$V_{OL}$	for an IO Pin		V <sub>DD</sub> = 3.3 V	I	_	0.3	V
	(I <sub>IO</sub> = +20 i	mA)	V <sub>DD</sub> = 3.63V		_	0.29	
	High level outpu	ıt voltage	V <sub>DD</sub> = 1.71V	1.48	_	_	
$V_{OH}$	for an 10 Pin		V <sub>DD</sub> = 3.3 V	3.17	_	_	V
	$(I_{IO} = +8 \text{ mA})$		V <sub>DD</sub> = 3.63V	3.47	_	_	
	High level output voltage		V <sub>DD</sub> = 1.71V		_	_	
Vон	foran 10 Pin		V <sub>DD</sub> = 3.3 V	2.96	_	_	V
	$(I_{IO} = +20 \text{ mA})$		V <sub>DD</sub> = 3.63V	3.26	_	_	
R <sub>PU</sub> <sup>(2)</sup>	Internal pull-up	All pins	_	_	40	_	kΩ
TYPU. /	resistor	PA10	_	_	10	_	N32
R <sub>PD</sub> <sup>(2)</sup>	Internal pull-	All pins	_	_	40	_	kΩ
LADV-	dow n resistor	PA10	_	_	10	_	NZZ

<sup>(1)</sup> Based on characterization, not tested in production.

Table 4-28. I/O port AC characteristics<sup>(1)(2)</sup>

GPIOx_MDy[1:0] bit value <sup>(3)</sup>	Parameter	Conditions	Max	Unit
GPIOx_CTL->MDy[1:0]=10 (IO_Speed = 2MHz)	Maximum	$1.8 \le V_{DD} \le 3.63 \text{ V}, C_L = 10 \text{ pF}$	4	
	Maximum frequency <sup>(4)</sup>	1.8 ≤ V <sub>DD</sub> ≤ 3.63 V, C <sub>L</sub> = 30 pF	3	MHz
		1.8 ≤ V <sub>DD</sub> ≤ 3.63 V, C <sub>L</sub> = 50 pF	2	
GPIOx_CTL->MDy[1:0] = 01 (IO_Speed = 10MHz)	Maximum frequency <sup>(4)</sup>	1.8 ≤ V <sub>DD</sub> ≤ 3.63 V, C <sub>L</sub> = 10 pF	60	
		1.8 ≤ V <sub>DD</sub> ≤ 3.63 V, C <sub>L</sub> = 30 pF	30	MHz
		$1.8 \le V_{DD} \le 3.63 \text{ V}, C_L = 50 \text{ pF}$	12	
GPIOx_CTL->MDy[1:0]=11	Maximum	$1.8 \le V_{DD} \le 3.63 \text{ V, } C_L = 10 \text{ pF}$	100	MHz

 $<sup>(2) \</sup>quad \text{Guaranteed by design, not tested in production.} \\$ 

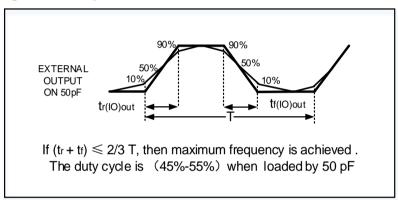
<sup>(3)</sup> All pins except PC13 / PC14 / PC15. Since PC13 to PC15 are supplied through the Power Switch, which can only be obtained by a small current, the speed of GPIOs PC13 to PC15 should not exceed 2 MHz when they are in output mode(maximum load: 30 pF).



GPIOx_MDy[1:0] bit value <sup>(3)</sup>	Parameter	Conditions	Max	Unit
(IO_Speed = 50MHz)	frequency <sup>(4)</sup>	$1.8 \le V_{DD} \le 3.63 \text{ V}, C_L = 30 \text{ pF}$	80	
		$1.8 \le V_{DD} \le 3.63 \text{ V}, C_L = 50 \text{ pF}$	60	
GPIOx_CTL->MDy[1:0]=11 and	Marrian	$1.8 \le V_{DD} \le 3.63 \text{ V}, C_L = 10 \text{ pF}$	120	
GPIOx_SPDy=1	Maximum frequency <sup>(4)</sup>	1.8 ≤ V <sub>DD</sub> ≤ 3.63 V, C <sub>L</sub> = 30 pF	100	MHz
(IO_Speed = MAX)	rrequency	1.8 ≤ V <sub>DD</sub> ≤ 3.63 V, C <sub>L</sub> = 50 pF	80	

- (1) Based on characterization, not tested in production.
- (2) Unless otherwise specified, all test results given for  $T_A = 25$  °C.
- (3) The I/O speed is configured using the GPIOx\_CTL -> MDy[1:0] bits. Refer to the GD32E50x user manual which is selected to set the GPIO port output speed.
- (4) The maximum frequency is defined in <u>Figure 4-5. I/O port AC characteristics definition</u>, and maximum frequency cannot exceed 180 MHz.

Figure 4-5. I/O port AC characteristics definition



## 4.13. Temperature sensor characteristics

Table 4-29. Temperature sensor characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Тур	Max	Unit
TL	VSENSE linearity with temperature	_	±1.5	_	°C
Avg_Slope	Average slope	_	4.1	_	mV/°C
V <sub>25</sub>	Voltage at 25 ℃	_	1.45	_	V
ts_temp <sup>(2)</sup>	ADC sampling time when reading the temperature	_	17.1	_	μs

- (1) Based on characterization, not tested in production.
- (2) Shortest sampling time can be determined in the application by multiple iterations.

#### 4.14. ADC characteristics

Table 4-30. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DDA</sub> <sup>(1)</sup>	Operating voltage	_	1.71	3.3	3.63	V
V <sub>IN</sub> <sup>(1)</sup>	ADC input voltage range	_	0	_	V <sub>REF+</sub>	V
V <sub>REFP</sub> <sup>(2)</sup>	Positive Reference Voltage	_	1.71	_	$V_{DDA}$	V
V <sub>REFN</sub> <sup>(2)</sup>	Negative Reference	_	_	$V_{SSA}$	_	٧



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	Voltage					
f <sub>ADC</sub> <sup>(1)</sup>	ADC clock	V <sub>DDA</sub> = 1.71 V to 2.4 V	0.1		14	MHz
TADC	ADC Clock	$V_{DDA} = 2.4 \text{ V to } 3.63 \text{ V}$	0.1	_	35	MHz
		12-bit	0.007		2.5	
fs <sup>(1)</sup>	Sampling rate	10-bit	0.008		2.92	MS
IS( ')		8-bit	0.01	_	3.5	PS
		6-bit	0.013	_	4.38	
V <sub>AIN</sub> <sup>(1)</sup>	Analog input voltage	16 external; 2 internal	0		$V_{DDA}$	V
R <sub>AIN</sub> <sup>(2)</sup>	External input impedance	See <u>Equation 2</u>	_	_	175.8	kΩ
R <sub>ADC</sub> <sup>(2)</sup>	Input sampling switch				0.5	kΩ
radc (=/	resistance				0.5	KL2
C <sub>ADC</sub> <sup>(2)</sup>	Input sampling capacitance	No pin/pad capacitance			4	рF
OADC**	input sampling capacitance	included			7	Pi
t <sub>CAL</sub> <sup>(2)</sup>	Calibration time	$f_{ADC} = 35 \text{ MHz}$	_	15.94	_	μs
t <sub>s</sub> (2)	Sampling time	$f_{ADC} = 35 \text{ MHz}$	0.043	_	6.84	μs
	Total assumation	12-bit	_	14	1	
<b>4</b> (2)	Total conversion	10-bit	_	12	_	1/
t <sub>CONV</sub> <sup>(2)</sup>	time(including sampling	8-bit	_	10	_	f <sub>ADC</sub>
	time)	6-bit	_	8	_	
t <sub>SU</sub> <sup>(2)</sup>	Startup time		_	_	1	μs

<sup>(1)</sup> Based on characterization, not tested in production.

#### Equation 2:

$$R_{AIN} \text{ max formula } R_{AIN} \! < \! \frac{T_s}{f_{ADC}{}^*C_{ADC}{}^*ln\left(2^{N+2}\right)} \! - \! R_{ADC}$$

The formula above (Equation 2) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 4-31. ADC  $R_{AIN}$  max for  $f_{ADC}$  = 35 MHz

T <sub>s</sub> (cycles)	t <sub>s</sub> (µs)	R <sub>AIN max</sub> (kΩ)
1.5	0.043	0.6
7.5	0.21	5.0
13.5	0.39	9.4
28.5	0.81	20.5
41.5	1.19	30.0
55.5	1.59	40.0
71.5	2.04	52.0
239.5	6.84	175.8

Table 4-32. ADC dynamic accuracy at  $f_{ADC}$  = 14 MHz  $V_{DDA}$  = 1.8  $V^{(1)}$ 

Sym bol	Parameter	Test conditions		Min	Тур	Max	Unit
ENOB	Effective number of bits	f <sub>ADC</sub> = 14 MHz	Single ended	10.4	10.8	_	bits

<sup>(2)</sup> Guaranteed by design, not tested in production.

# GD32E503xxDatasheet

Symbol 5 contracts	Parameter	Test condit	Test conditions		Тур	Max	Unit
		$V_{DDA} = V_{REFP} = 1.8 \text{ V}$	Differential	10.9	11.3	_	
SVIDB	Signal-to-noise and	Input Frequency = 20	Single ended	64.4	66.8	_	
SNDR	distortion ratio	kHz	Differential	67.5	69.9	_	
CVID	Signal to poince ratio		Single ended	64.5	66.9	_	dB
SINK	SNR Signal-to-noise ratio		Differential	67.6	70.2	_	иБ
TUD	Total harmonic		Single ended	_	-81	-78	
THD	distortion		Differential		-82	-79	

<sup>(1)</sup> Based on characterization, not tested in production.

#### Table 4-33. ADC dynamic accuracy at $f_{ADC} = 35 \text{ MHz V}_{DDA} = 3.3 \text{ V}^{(1)}$

Sym bol	Parameter	Test condit	ions	Min	Тур	Max	Unit
ENOB			Single ended	10.7	11.1		hita
	Effective number of bits		Differential	11	11.4	_	bits
SNIDD	Signal-to-noise and	f <sub>ADC</sub> = 35 MHz	Single ended	66.2	68.6	_	
SNDR	distortion ratio	$V_{DDA} = V_{REFP} = 3.3 \text{ V}$	Differential	68.2	70.6	_	
SNR	Signal to poince ratio	Input Frequency = 20	Single ended	66	68.8	_	dB
SINK	Signal-to-noise ratio	kHz	Differential	68	71	_	иБ
TUD	Total harmonic		Single ended		-82	-78	
THD	distortion		Differential	1	-83	-79	

<sup>(1)</sup> Based on characterization, not tested in production.

#### Table 4-34. ADC dynamic accuracy at $f_{ADC} = 35 \text{ MHz V}_{DDA} = 2.4 \text{ V}^{(1)}$

Symbol	Parameter	Test condit	ions	Min	Тур	Max	Unit
ENOB Eff	Effective would be of hite		Single ended	10.6	11	_	la :4a
	Effective number of bits		Differential	11	11.4	_	bits
SNDR	Signal-to-noise and	f <sub>ADC</sub> = 35 MHz	Single ended	66	68.3	_	
SNDR	distortion ratio	V <sub>DDA</sub> = V <sub>REFP</sub> =2.4 V	Differential	68	70.4	_	
SNR	Oine al tamaia a matia	Input Frequency = 20	Single ended	65	68.5	_	dB
SINK	Signal-to-noise ratio	kHz	Differential	67	70.8		uБ
TIID	Total harmonic		Single ended		-82	-78	
THD	distortion		Differential		-83	-79	

<sup>(1)</sup> Based on characterization, not tested in production.

### Table 4-35. ADC static accuracy at $f_{ADC}$ = 14 MHz $V_{DDA}$ = 1.8 $V^{(1)}$

Sym bol	Parameter	Test condi	Test conditions		Max	Unit
Offset	Offset error		Single ended	±0.5	±1	
Oriset	Orrseterror		Differential	±0.5	±1	
DNL	Differential linearity	f <sub>ADC</sub> = 14 MHz	Single ended	±0.5	±1	LSB
DINL	error	$V_{DDA} = V_{REFP} = 1.8 \text{ V}$	Differential	±0.6	±1	LOD
INL	lata and the soit and		Single ended	±0.6	±1	
IINL	Integral linearity error		Differential	±0.8	±1.5	

<sup>(1)</sup> Based on characterization, not tested in production.



Table 4-36. ADC static accuracy at  $f_{ADC} = 35 \text{ MHz V}_{DDA} = 3.3 \text{ V}^{(1)}$ 

Table 1 colling a country at 1,200 colling 1 bbA								
Sym bol	Parameter	Test condi	itions	Тур	Max	Unit		
Official	Officetown		Single ended	±0.5	±1			
Offset	Offset error		Differential	±0.5	±1			
DNL	Differential linearity	f <sub>ADC</sub> = 35 MHz	Single ended	±0.5	±0.8	LSB		
DINL	error	$V_{DDA} = V_{REFP} = 3.3 \text{ V}$	Differential	±0.7	±1	LOD		
IN II	late and linearity orner		Single ended	±0.7	±1			
INL	Integral linearity error		Differential	±0.9	±1.5			

<sup>(1)</sup> Based on characterization, not tested in production.

Table 4-37. ADC static accuracy at  $f_{ADC}$  = 35 MHz  $V_{DDA}$  = 2.4  $V^{(1)}$ 

Symbol 5 contracts	Parameter	Test condi	itions	Тур	Max	Unit
Offset	Offset error		Single ended	±0.5	±1	
Onset	Offset error		Differential	±0.5	±1	
DN II	Differential linearity	f <sub>ADC</sub> = 35 MHz	Single ended	±0.5	±0.8	LCD
DNL	NL error	$V_{DDA} = V_{REFP} = 2.4 \text{ V}$	Differential	±0.6	±1	LSB
INL			Single ended	±0.6	±1	
	Integral linearity error		Differential	±0.8	±1.5	

<sup>(1)</sup> Based on characterization, not tested in production.



## 4.15. DAC characteristics

Table 4-38. DAC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DDA</sub> <sup>(1)</sup>	Operating voltage	_	1.8	3.3	3.63	V
V <sub>REFP</sub> <sup>(2)</sup>	Positive Reference Voltage	_	1.8	_	$V_{DDA}$	٧
V <sub>REFN</sub> <sup>(2)</sup>	Negative Reference Voltage	_		V <sub>SSA</sub>	-	V
R <sub>LOAD</sub> <sup>(2)</sup>	Load resistance	Resistive load with buffer ON		_	_	kΩ
Ro <sup>(2)</sup>	Impedance output with buffer OFF	_	_	_	15	kΩ
C <sub>LOAD</sub> <sup>(2)</sup>	Load capacitance	No pin/pad capacitance included		_	50	pF
DAC_OUT min <sup>(2)</sup>	Low er DAC_OUT voltage with buffer ON	_	0.2	_	-	٧
DAC_OUT max <sup>(2)</sup>	Higher DAC_OUT voltage with buffer ON	_	_	_	VDDA -0.2	V
DAC_OUT min <sup>(2)</sup>	Low er DAC_OUT voltage w ith buffer OFF	_		0.5	1	mV
DAC_OUT max <sup>(2)</sup>	Higher DAC_OUT voltage with buffer OFF	_	_	_	VREF -1LSB	٧
I <sub>DDA</sub> (1)	DAC current consumption	With no load, middle code(0x800) on the input, $V_{REF+} = 3.63 \text{ V}$		400	_	uA
IDDA\ /	in quiescent mode	With no load, worst code(0xF1C) on the input, $V_{REF+} = 3.63 \text{ V}$	l	450	ı	uA
IDDVREF+(1)	DAC current consumption	With no load, middle code(0x800) on the input, $V_{REF+} = 3.63 \text{ V}$		100	1	uA
IDDVREF+\	in quiescent mode	With no load, worst code(0xF1C) on the input, $V_{REF+} = 3.63 \text{ V}$		150	1	uA
DNL <sup>(1)</sup>	Differential non-linearity error	DAC in 12-bit mode			±2	LSB
INL <sup>(1)</sup>	Integral non-linearity	DAC in 12-bit mode	_	_	±4	LSB
Offset <sup>(1)</sup>	Offset error	DAC in 12-bit mode	_	_	10	LSB
GE <sup>(1)</sup>	Gain error	DAC in 12-bit mode	_	_	0.5	%
T <sub>setting</sub> <sup>(1)</sup>	Settling time	C <sub>LOAD</sub> ≤ 50 pF, R <sub>LOAD</sub> ≥ 5 kΩ	_	_	0.5	μs
T <sub>wakeup</sub> <sup>(2)</sup>	Wakeup from off state	_	_		5	μs
Update rate <sup>(2)</sup>	Max frequency for a correct DAC_OUT change from code i to i±1LSBs	C <sub>LOAD</sub> ≤ 50 pF, R <sub>LOAD</sub> ≥ 5 kΩ	_	_	4	MS/s
PSRR <sup>(2)</sup>	Pow er supply rejection	_	55	80	_	dB



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	ratio					
	(to V <sub>DDA</sub> )					

- (1) Based on characterization, not tested in production.
- (2) Guaranteed by design, not tested in production.

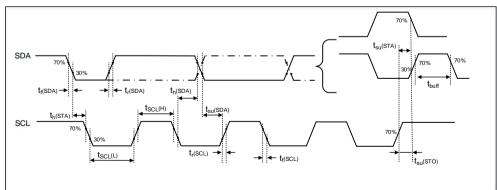
#### 4.16. I2C characteristics

Table 4-39. I2C characteristics(1)(2)

Symbol	Parameter	Condition	Standard	dmode	Fast mode		Fast mode plus		Unit
		S	Min	Max	Min	Max	Min	Max	
t <sub>SCL(H)</sub>	SCL clock high time		4.0	_	0.6	_	0.2		μs
t <sub>SCL(L)</sub>	SCL clock low time		4.7		1.3	_	0.5		μs
t <sub>su(SDA)</sub>	SDA setup time		250	_	100		50	1	ns
t <sub>h(SDA)</sub>	SDA data hold time		0(3)	3450	0	900	0	450	ns
t <sub>r</sub> (SDA/SCL)	SDA and SCL rise time		l	1000		300		120	ns
t <sub>f(SDA/SCL)</sub>	SDA and SCL fall time			300		300		120	ns
t <sub>h(STA)</sub>	Start condition hold time		4.0	_	0.6	_	0.26	_	μs

- $(1) \quad \text{Guaranteed by design, not tested in production.}$
- (2) To ensure the standard mode I2C frequency, f<sub>PCLK1</sub> must be at least 2 MHz. To ensure the fast mode I2C frequency, f<sub>PCLK1</sub> must be at least 4 MHz. To ensure the fast mode plus I2C frequency, f<sub>PCLK1</sub> must be at least a multiple of 10 MHz.
- (3) The device should provide a data hold time of 300 ns at least in order to bridge the undefined region of the falling edge of SCL.

Figure 4-6. I2C bus timing diagram



### 4.17. SPI characteristics

Table 4-40. Standard SPI characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit

# GD32E503xxDatasheet

95022000/M544401100						
fsck	SCK clock frequency	_	_	_	22.5	MHz
tsck(H)	SCK clock high time	Master mode, $f_{PCLKx}$ = 90 MHz, presc = 4		22.2		ns
t <sub>SCK(L)</sub>	SCK clock low time	Master mode, f <sub>PCLKx</sub> = 90 MHz, presc = 4		22.2		ns
		SPI master mode				
t <sub>V(MO)</sub>	Data output valid time	_	_	_	10	ns
t <sub>SU(MI)</sub>	Data input setup time	_	1	_	_	ns
t <sub>H(MI)</sub>	Data input hold time	_	0			ns
		SPI slave mode				
t <sub>SU(NSS)</sub>	NSS enable setup time	_	0	_	_	ns
t <sub>H(NSS)</sub>	NSS enable hold time	_	1	_	_	ns
t <sub>A(SO)</sub>	Data output access time	_	_	10	_	ns
t <sub>DIS(SO)</sub>	Data output disable time		_	11		ns
t <sub>V(SO)</sub>	Data output valid time	_	_	11	_	ns
t <sub>SU(SI)</sub>	Data input setup time	_	0	_	_	ns
t <sub>H(SI)</sub>	Data input hold time	_	1	_	_	ns

<sup>(1)</sup> Based on characterization, not tested in production.

Figure 4-7. SPI timing diagram - master mode

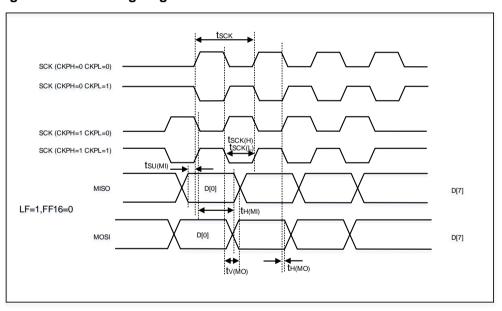
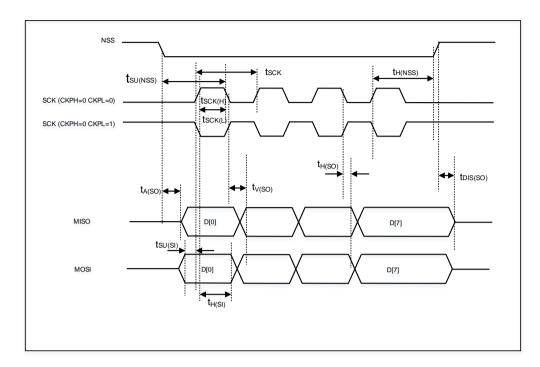




Figure 4-8. SPI timing diagram - slave mode





## 4.18. I2S characteristics

Table 4-41. I2S characteristics<sup>(1)(2)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode (data: 32 bits,	_	6.21	_	
f <sub>CK</sub>	Clock frequency	Audio frequency = 96 kHz)			12.5	MHz
	<u>.</u>	Slave mode	_		12.5	
t <sub>H</sub>	Clock high time	_	_	81	_	ns
t∟	Clock low time		_	81	_	ns
t <sub>V(WS)</sub>	WS valid time	Master mode		3		ns
t <sub>H(WS)</sub>	WS hold time	Master mode	_	3	_	ns
t <sub>SU(WS)</sub>	WS setup time	Slave mode	0	_	_	ns
t <sub>H(WS)</sub>	WS hold time	Slave mode	2	_	_	ns
_	I2S slave input clock duty	Q1 .				0.4
Ducy <sub>(SCK)</sub>	cycle	Slave mode	_	50	_	%
tsu(SD_MR)	Data input setup time	Master mode	1	_	_	ns
tsu(sd_sr)	Data input setup time	Slave mode	0	_	_	ns
t <sub>H(SD_MR)</sub>	Data input hold time	Master receiver	0	_	_	ns
t <sub>H(SD_SR)</sub>	Data input hold time	Slave receiver	1	_	_	ns
1	Data autout valid time	Slave transmitter			10	
t <sub>V(SD_ST)</sub>	Data output valid time	(after enable edge)	_	_	10	ns
	Data autout hald time	Slave transmitter	3			
t <sub>H(SD_ST)</sub>	Data output hold time	(after enable edge)	3	_		ns
	Data autout valid Con	Master transmitter			40	
t∨(SD_MT)	Data output valid time	(after enable edge)	_		10	ns
t.,,,,,,,,,,,	Data autout hold time	Master transmitter	0			no
th(SD_MT)	Data output hold time	(after enable edge)	0	_	_	ns

<sup>(1)</sup> Guaranteed by design, not tested in production.

<sup>(2)</sup> Based on characterization, not tested in production



Figure 4-9. I2S timing diagram - master mode

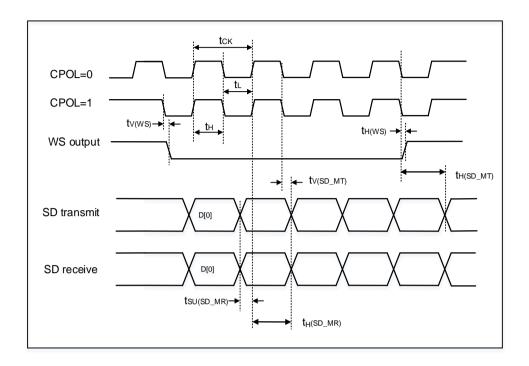
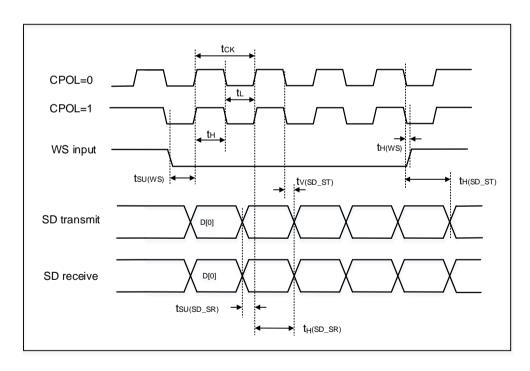


Figure 4-10. I2S timing diagram - slave mode





### 4.19. USART characteristics

Table 4-42. USART characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fsck	SCK clock frequency	f <sub>PCLKx</sub> = 180 MHz			90	MHz
t <sub>SCK(H)</sub>	SCK clock high time	f <sub>PCLKx</sub> = 180 MHz	5	_	_	ns
tsck(L)	SCK clock low time	f <sub>PCLKx</sub> = 180 MHz	5	_	_	ns

<sup>(1)</sup> Guaranteed by design, not tested in production.

### 4.20. USBD characteristics

Table 4-43. USBD start up time

Symbol	Parameter	Max	Unit
tstartup <sup>(1)</sup>	USBD startup time	1	μs

<sup>(1)</sup> Guaranteed by design, not tested in production.

Table 4-44. USBD DC electrical characteristics

Symbol		Parameter	Conditions	Min	Тур	Max	Unit
	$V_{DD}$	USBFS operating voltage	_	3		3.63	
Input	$V_{DI}$	Differential input sensitivity	_	0.2		_	V
levels <sup>(1)</sup>	$V_{\text{CM}}$	Differential common mode range	Includes V <sub>DI</sub> range	0.8		2.5	V
	$V_{\text{SE}}$	Single ended receiver threshold	_	8.0		2.0	
Output	$V_{\text{OL}}$	Static output level low	$R_L$ of 1.0 $k\Omega$ to 3.63 $V$		_	0.3	V
levels (2)	V <sub>OH</sub>	Static output level high	$R_L$ of 15 $k\Omega$ to $V_{SS}$	2.8	3.3	3.63	٧

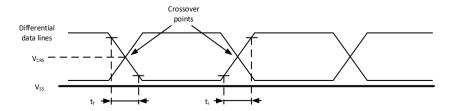
<sup>(1)</sup> Guaranteed by design, not tested in production.

Table 4-45. USBD full speed-electrical characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>R</sub>	Rise time	CL = 50 pF	4	5	20	ns
t <sub>F</sub>	Fall time	CL = 50 pF	4	5	20	ns
t <sub>RFM</sub>	Rise/ fall time matching	t <sub>R</sub> / t <sub>F</sub>	90		110	%
VCRS	Output signal crossover voltage	_	1.3		2.0	V

<sup>(1)</sup> Guaranteed by design, not tested in production.

Figure 4-11. USBD timings: definition of data signal rise and fall time



<sup>(2)</sup> Based on characterization, not tested in production.



### 4.21. SDIO characteristics

Table 4-46. SDIO characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
f <sub>PP</sub> (3)	Clock frequency in data transfer mode	_	0	_	48	MHz		
tw(ckl) (3)	Clock low time	f <sub>pp</sub> = 48 MHz	10.5	11	_	ns		
t <sub>W(CKH)</sub> (3)	Clock high time	f <sub>pp</sub> = 48 MHz	9.5	10	_	ns		
	CMD, D inputs (referenced to C	CK) in MMC and S	D HS mo	de				
t <sub>ISU</sub> <sup>(4)</sup>	Input setup time HS	f <sub>pp</sub> = 48 MHz	4	_	_	ns		
t <sub>IH</sub> <sup>(4)</sup>	Input hold time HS	$f_{pp} = 48 \text{ MHz}$	3	_	_	ns		
	CMD, D outputs (referenced to CK) in MMC and SD HS mode							
tov <sup>(3)</sup>	Output valid time HS	$f_{pp} = 48 \text{ MHz}$	-	_	13.8	ns		
toH <sup>(3)</sup>	Output hold time HS	$f_{pp} = 48 \text{ MHz}$	12	_		ns		
	CMD, D inputs (referenced	to CK) in SD defa	ult mode					
t <sub>ISUD</sub> (4)	Input setup time SD	$f_{pp} = 24 \text{ MHz}$	3	_		ns		
t <sub>IHD</sub> (4)	Input hold time SD	f <sub>pp</sub> = 24 MHz	3	_	_	ns		
	CMD, D outputs (referenced to CK) in SD default mode							
t <sub>OVD</sub> (3)	Output valid default time SD	$f_{pp} = 24 \text{ MHz}$	_	2.4	2.8	ns		
t <sub>OHD</sub> (3)	Output hold default time SD	f <sub>pp</sub> = 24 MHz	0.8		_	ns		

<sup>(1)</sup> CLK timing is measured at 50% of  $V_{\mbox{\scriptsize DD}}.$ 

### 4.22. EXMC characteristics

Table 4-47. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings<sup>(1)(2)(3)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	EXMC_NE low time	27	29	ns
t <sub>V(NOE_NE)</sub>	EXMC_NEx low to EXMC_NOE low	0		ns
t <sub>w(NOE)</sub>	EXMC_NOE low time	27	29	ns
t <sub>h(NE_NOE)</sub>	EXMC_NOE high to EXMC_NE high hold time	0		ns
t <sub>v(A_NE)</sub>	EXMC_NEx low to EXMC_A valid	0	_	ns
t <sub>V(BL_NE)</sub>	EXMC_NEx low to EXMC_BL valid	0	1	ns
t <sub>su(DATA_NE)</sub>	Data to EXMC_NEx high setup time	21.4	ı	ns
t <sub>su(DATA_NOE)</sub>	Data to EXMC_NOEx high setup time	21.4	1	ns
t <sub>h(DATA_NOE)</sub>	Data hold time after EXMC_NOE high	0		ns
t <sub>h(DATA_NE)</sub>	Data hold time after EXMC_NEx high	0		ns
t <sub>v(NADV_NE)</sub>	EXMC_NEx low to EXMC_NADV low	0	_	ns
t <sub>w(NADV)</sub>	EXMC_NA DV low time	4.6	6.6	ns

<sup>(1)</sup>  $C_L = 30 \text{ pF}.$ 

<sup>(2)</sup> Capacitive load  $C_L = 30 \text{ pF}.$ 

<sup>(3)</sup> Based on characterization, not tested in production.

<sup>(4)</sup> Guaranteed by design, not tested in production

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(3)</sup> Based on configure:  $f_{HCLK} = 180 \text{ MHz}$ , AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.



Table 4-48. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings (1)(2)(3)

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	EXMC_NE low time	15.8	17.8	ns
t <sub>V(NWE_NE)</sub>	EXMC_NEx low to EXMC_NWE low	4.6		ns
t <sub>w(NWE)</sub>	EXMC_NWE low time	4.6	6.6	ns
t <sub>h(NE_NWE)</sub>	EXMC_NWE high to EXMC_NE high hold time	4.6	6.6	ns
t <sub>v(A_NE)</sub>	EXMC_NEx low to EXMC_A valid	0	_	ns
t <sub>V(NADV_NE)</sub>	EXMC_NEx low to EXMC_NADV low	0	_	ns
t <sub>w(NADV)</sub>	EXMC_NA DV low time	4.6	6.6	ns
t <sub>h(AD_NADV)</sub>	EXMC_AD(address) valid hold time after  EXMC_NADV high	10.2		ns
t <sub>h(A_NWE)</sub>	Address hold time after EXMC_NWE high	4.6	_	ns
t <sub>h(BL_NWE)</sub>	EXMC_BL hold time after EXMC_NWE high	4.6	_	ns
t <sub>v(BL_NE)</sub>	EXMC_NEx low to EXMC_BL valid	15.8 17.8		ns
t <sub>v(DATA_NADV)</sub>	EXMC_NA DV high to DATA valid 4.6 —		_	ns
t <sub>h(DATA_NWE)</sub>	Data hold time after EXMC_NWE high	4.6	6.6	ns

<sup>(1)</sup>  $C_L = 30 pF$ .

Table 4-49. Asynchronous multiplexed PSRAM/NOR read timings (1)(2)(3)

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	EXMC_NE low time	38.2	40.2	ns
t <sub>V(NOE_NE)</sub>	EXMC_NEx low to EXMC_NOE low	15.8	_	ns
t <sub>w(NOE)</sub>	EXMC_NOE low time	21.4	23.4	ns
t <sub>h(NE_NOE)</sub>	EXMC_NOE high to EXMC_NE high hold time	0	ı	ns
t <sub>v(A_NE)</sub>	EXMC_NEx low to EXMC_A valid	0	1	ns
t <sub>v(A_NOE)</sub>	Address hold time after EXMC_NOE high	0		ns
t <sub>v(BL_NE)</sub>	EXMC_NEx low to EXMC_BL valid	0	1	ns
t <sub>h(BL_NOE)</sub>	EXMC_BL hold time after EXMC_NOE high	0	1	ns
t <sub>su(DATA_NE)</sub>	Data to EXMC_NEx high setup time	22.4	_	ns
t <sub>su(DATA_NOE)</sub>	Data to EXMC_NOEx high setup time	22.4	_	ns
t <sub>h(DATA_NOE)</sub>	Data hold time after EXMC_NOE high	0	_	ns
t <sub>h(DATA_NE)</sub>	Data hold time after EXMC_NEx high	0	_	ns
t <sub>v(NADV_NE)</sub>	EXMC_NEx low to EXMC_NADV low	0	_	ns
t <sub>w(NADV)</sub>	EXMC_NA DV low time	4.6	6.6	ns
T <sub>h(AD_NADV)</sub>	EXMC_AD(adress) valid hold time after		6.6	ns

<sup>(1)</sup>  $C_L = 30 pF$ .

Table 4-50. Asynchronous multiplexed PSRAM/NOR write timings (1)(2)(3)

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	EXMC_NE low time	27	29	ns

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(3)</sup> Based on configure: f<sub>HCLK</sub> = 180 MHz, AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.

 $<sup>(2) \</sup>quad \text{Guaranteed by design, not tested in production.} \\$ 

 $<sup>(3) \</sup>quad \text{Based on configure: } f_{\text{HCLK}} = 180 \text{ MHz}, \\ \text{AddressSetupTime} = 0, \\ \text{AddressHoldTime} = 1, \\ \text{DataSetupTime} = 1.$ 



t <sub>V(NWE_NE)</sub>	EXMC_NEx low to EXMC_NWE low 7.3			ns
t <sub>w(NWE)</sub>	EXMC_NWE low time	15.8	17.8	ns
t <sub>h(NE_NWE)</sub>	EXMC_NWE high to EXMC_NE high hold time	4.6	_	ns
t <sub>v(A_NE)</sub>	EXMC_NEx low to EXMC_A valid	0	_	ns
t <sub>V(NADV_NE)</sub>	EXMC_NEx low to EXMC_NADV low	0	ı	ns
t <sub>w(NADV)</sub>	EXMC_NA DV low time	4.6	6.6	ns
t. (40 MAD) 0	EXMC_AD(address) valid hold time after	4.6		ns
t <sub>h(AD_NADV)</sub>	EXMC_NA DV high	4.0		115
t <sub>h(A_NWE)</sub>	Address hold time after EXMC_NWE high	4.6	ı	ns
t <sub>h(BL_NWE)</sub>	EXMC_BL hold time after EXMC_NWE high	4.6	1	ns
t <sub>v(BL_NE)</sub>	EXMC_NEx low to EXMC_BL valid	0		ns
t <sub>v(DATA_NADV)</sub>	EXMC_NA DV high to DATA valid 4.6 —		_	ns
t <sub>h(DATA_NWE)</sub>	Data hold time after EXMC_NWE high	4.6	_	ns

<sup>(1)</sup>  $C_L = 30 pF$ .

Table 4-51. Synchronous multiplexed PSRAM/NOR read timings<sup>(1)(2)(3)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	EXMC_CLK period	22.4 —	_	ns
t <sub>d(CLKL-NExL)</sub>	EXMC_CLK low to EXMC_NEx low	0	ı	ns
t <sub>d(CLKH-NExH)</sub>	EXMC_CLK high to EXMC_NEx high	10.2	ı	ns
t <sub>d(CLKL-NADVL)</sub>	EXMC_CLK low to EXMC_NA DV low	0	ı	ns
t <sub>d(CLKL-NADVH)</sub>	EXMC_CLK low to EXMC_NA DV high	0		ns
t <sub>d(CLKL-AV)</sub>	EXMC_CLK low to EXMC_Ax valid	0		ns
t <sub>d(CLKH-AIV)</sub>	EXMC_CLK high to EXMC_Ax invalid	10.2		ns
t <sub>d(CLKL-NOEL)</sub>	EXMC_CLK low to EXMC_NOE low	0		ns
t <sub>d(CLKH-NOEH)</sub>	EXMC_CLK high to EXMC_NOE high	10.2	_	ns
t <sub>d(CLKL-ADV)</sub>	EXMC_CLK low to EXMC_A D valid	0	_	ns
t <sub>d(CLKL-ADIV)</sub>	EXMC_CLK low to EXMC_A D invalid	0	_	ns

<sup>(1)</sup>  $C_L = 30 pF$ .

Table 4-52. Synchronous multiplexed PSRAM write timings<sup>(1)(2)(3)</sup>

	-	_		
Symbol	Parameter Min		Max	Unit
t <sub>w(CLK)</sub>	EXMC_CLK period	22.4	_	ns
t <sub>d(CLKL-NExL)</sub>	EXMC_CLK low to EXMC_NEx low	0	_	ns
t <sub>d(CLKH-NExH)</sub>	EXMC_CLK high to EXMC_NEx high	10.2	_	ns
t <sub>d(CLKL-NADVL)</sub>	EXMC_CLK low to EXMC_NA DV low	0	_	ns
t <sub>d(CLKL-NADVH)</sub>	EXMC_CLK low to EXMC_NA DV high	0	_	ns
t <sub>d(CLKL-AV)</sub>	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t <sub>d(CLKH-AIV)</sub>	EXMC_CLK high to EXMC_Ax invalid	10.2	_	ns
t <sub>d(CLKL-NWEL)</sub>	EXMC_CLK low to EXMC_NWE low	0	_	ns

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(3)</sup> Based on configure:  $f_{HCLK} = 180 \text{ MHz}$ , AddressSetupTime = 0, AddressHoldTime = 1, DataSetupTime = 1.

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(3)</sup> Based on configure: f<sub>HCLK</sub> = 180 MHz, BurstAccessMode = Enable; Memory Type = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC\_CLK is 4 divided by HCLK); Data Latency = 1.

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Symbol	Parameter	Min	Max	Unit
t <sub>d(CLKH-NWEH)</sub>	EXMC_CLK high to EXMC_NWE high	10.2		ns
t <sub>d(CLKL-ADIV)</sub>	EXMC_CLK low to EXMC_A D invalid	0	_	ns
td(CLKL-DATA)	EXMC_A/D valid data after EXMC_CLK low 0			ns
t <sub>h(CLKL-NBLH)</sub>	EXMC_CLK low to EXMC_NBL high	0	_	ns

<sup>(1)</sup>  $C_L = 30 pF$ .

- (2) Guaranteed by design, not tested in production.
- (3) Based on configure: f<sub>HCLK</sub> = 180 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC\_CLK is 4 divided by HCLK); DataLatency = 1.

Table 4-53. Synchronous non-multiplexed PSRAM/NOR read timings(1)(2)(3)

Symbol	Param eter M		Max	Unit
t <sub>w(CLK)</sub>	EXMC_CLK period	22.4		ns
t <sub>d(CLKL-NExL)</sub>	EXMC_CLK low to EXMC_NEx low	0	_	ns
t <sub>d(CLKH-NExH)</sub>	EXMC_CLK high to EXMC_NEx high	10.2	ı	ns
t <sub>d(CLKL-NADVL)</sub>	EXMC_CLK low to EXMC_NA DV low	0	ı	ns
t <sub>d(CLKL-NADVH)</sub>	EXMC_CLK low to EXMC_NA DV high	0	1	ns
t <sub>d(CLKL-AV)</sub>	EXMC_CLK low to EXMC_Ax valid	0		ns
t <sub>d(CLKH-AIV)</sub>	EXMC_CLK high to EXMC_Ax invalid	10.2		ns
t <sub>d(CLKL-NOEL)</sub>	EXMC_CLK low to EXMC_NOE low	0	_	ns
t <sub>d(CLKH-NOEH)</sub>	EXMC_CLK high to EXMC_NOE high	10.2	_	ns

<sup>(1)</sup>  $C_L = 30 pF$ .

- (2) Guaranteed by design, not tested in production.
- (3) Based on configure: HCLK=180 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC\_CLK is 4 divided by HCLK); DataLatency = 1.

Table 4-54. Synchronous non-multiplexed PSRAM write timings<sup>(1)(2)(3)</sup>

Symbol	Parameter Min		Max	Unit
t <sub>w(CLK)</sub>	EXMC_CLK period	22.4	ı	ns
t <sub>d(CLKL-NExL)</sub>	EXMC_CLK low to EXMC_NEx low	0		ns
t <sub>d(CLKH-NExH)</sub>	EXMC_CLK high to EXMC_NEx high	10.2	ı	ns
t <sub>d(CLKL-NADVL)</sub>	EXMC_CLK low to EXMC_NA DV low	0		ns
t <sub>d(CLKL-NADVH)</sub>	EXMC_CLK low to EXMC_NA DV high	0		ns
t <sub>d(CLKL-AV)</sub>	EXMC_CLK low to EXMC_Ax valid	0	_	ns
t <sub>d(CLKH-AIV)</sub>	EXMC_CLK high to EXMC_Ax invalid	10.2		ns
t <sub>d(CLKL-NWEL)</sub>	EXMC_CLK low to EXMC_NWE low	0	_	ns
t <sub>d(CLKH-NWEH)</sub>	EXMC_CLK high to EXMC_NWE high	10.2	_	ns
t <sub>d(CLKL-DATA)</sub>	EXMC_A/D valid data after EXMC_CLK low	0		ns
t <sub>h(CLKL-NBLH)</sub>	EXMC_CLK low to EXMC_NBL high	0		ns

<sup>(1)</sup>  $C_L = 30 pF$ .

- (2) Guaranteed by design, not tested in production.
- (3) Based on configure: HCLK = 180 MHz, BurstAccessMode = Enable; MemoryType = PSRAM; WriteBurst = Enable; CLKDivision = 3 (EXMC\_CLK is 4 divided by HCLK); DataLatency = 1.



## 4.23. Serial/Quad Parallel Interface (SQPI) characteristics

Table 4-55.SQPI characteristics

Symbol	Parameter	Min	Тур	Max	Unit
t <sub>CLK</sub> <sup>(2)</sup>	CLK period	11.0 <sup>(4)</sup>	ı	ı	ns
t <sub>CD</sub> <sup>(2)</sup>	CLK high level duty for even clock divided	45	50	55	%
rCD(=)	CLK high level duty for odd clock divided	45	-	71	%
t <sub>KHKL</sub> (3)	CLK rise or fall time	_		3	ns
t <sub>CPH</sub> <sup>(2)</sup>	CE# high between subsequent burst operations	22.2	-	-	ns
t <sub>CEM</sub> <sup>(2)</sup>	CE# low pulse width	88.8	_	_	ns
t <sub>CSP</sub> <sup>(2)</sup>	CE# setup time to CLK rising edge	5.5	-	177.7	ns
t <sub>CHD</sub> <sup>(2)</sup>	CE# hold time from CLK rising edge	5.5	_	177.7	ns
tsP <sup>(2)</sup>	Setup time to active CLK edge	5.5	_	177.7	ns
t <sub>HD</sub> <sup>(2)</sup>	Hold time from active CLK edge	5.5	ı	177.7	ns
t <sub>HZ</sub> (2)	CE# rise to data output high-Z	_	0		ns
t <sub>ACLK</sub> (2)	CLK fall to data output valid delay	_	0	_	ns
t <sub>KOH</sub> (2)	Data hold time from CLK falling edge	_	0	_	ns

<sup>(1)</sup> Based on characterization, not tested in production.

## 4.24. Super High-resolution Timer (SHRTIMER) characteristics

Table 4-56. SHRTIMER characteristics(1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>SHRTIMER</sub>	SHRTIMER input clock	Under T <sub>A</sub> conditions	_	180	_	MHz
tshrtimer	for DLL	Onder 14 conditions		5.56	_	ns
t <sub>res(SHRTIMER)</sub>	Timer resolution time	f <sub>HPMER</sub> = 180 MHz		86.8		ps
RESSHRTIMER	Timer resolution	ı			16	bit
4	Dead time generator	ı	1/64		16	tshrtimer
t <sub>DTG</sub>	clock period	f <sub>SHRTIMER</sub> =180 MHz	0.0868		88.89	ns
H	Dead time range	_	_	_	2^16-1	t <sub>DTG</sub>
t <sub>DTR</sub>  / t <sub>DTF</sub>	(absolute value)	f <sub>SHRTIMER</sub> =180 MHz	_	_	5825.41	μs
f	Chopper stage clock	_	1/256	_	1/16	f <sub>SHRTIMER</sub>
f <sub>CHPFRQ</sub>	frequency	f <sub>SHRTIMER</sub> = 180 MHz	0.703		11.25	MHz
	Chopper first pulse	_	16	_	256	tshrtimer
t <sub>1STPW</sub>	length	f <sub>SHRTIMER</sub> =180 MHz	0.089	_	1.42	μs

<sup>(1)</sup> Guaranteed by design, not tested in production.

<sup>(2)</sup> Guaranteed by design, not tested in production.

<sup>(3)</sup> Output driven mode is 50 MHz. Measured from 10% to 90% of VDD.

<sup>(4)</sup> This is designed minimal period. The operating minimal clock period is 22.2 ns (45 MHz = 180 MHz/4).



Table 4-57. SHRTIMER output response to fault protection<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>LAT(DF)</sub>	Digital fault response latency	Propagation delay from SHRTIMER_FLTx digital input to SHRTIMER_STx CHy output pin	l	l	25	
tw(FLT)	Minimum fault pulse width	_	11	_	_	ns
t <sub>LAT(AF)</sub>	Analog fault response latency	Propagation delay from comparator  CMPx_IPx input to  SHRTIMER_STx CHy output pin			35	

<sup>(1)</sup> Guaranteed by design, not tested in production.

Table 4-58. SHRTIMER output response to external 1 to 10(Synchronous mode<sup>(1)</sup>)

Symbol	Param eter Param eter	Conditions	Min	Тур	Max	Unit
TPROP(SHRTIMER)	External event response latency in SHRTIMER	SHRTIMER internal propagation delay <sup>(3)</sup>	5	_	6	t <sub>SHRTIMER</sub> (2 )
t <sub>LAT(DEEV)</sub>	Digital external event response latency	Propagation delay from SHRTIMER_EXEVx digital input to SHRTIMER_STx CHy output pin(30pF load)		_	48	
t <sub>W(FLT)</sub>	Minimum external event pulse width	_	11	_	_	ns
tlat(AEEV)	Analog external event response latency	Propagation delay from comparator CMPx_IPx input pin to SHRTIMER_STx.CHy output pin(30pF load)	ı	_	60	
T <sub>JIT(EEV)</sub>	External event response jitter	Jitter of the delay from SHRTIMER_EXEVx digital input or CMPx_IPx input pin to SHRTIMER_STx CHy output pin(30pF load)	_	_	1	tshrtimer <sup>(2</sup> )
T <sub>JIT(PW)</sub>	Jitter on output pulse widthin response to an external event	put pulse onse to an —		_	0	tshrtimer <sup>(2</sup> )

<sup>(1)</sup> Guaranteed by design, not tested in production.

<sup>(2)</sup>  $t_{SHRTIMER} = 1/f_{SHRTIMER}$  with  $t_{SHRTIMER} = 180$  MHz depending on the clock controller configuration.

 $<sup>(3) \</sup>quad \text{This parameter does not take into account latency introduced by GPIO or comparator.}$ 



Table 4-59. SHRTIMER synchronization input / output<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
taronacono	Minimum pulse width on SYNCIN		2		_	t <sub>SHRTIMER</sub> (2
tw(syncin)	inputs, including SHRTIMER_SCIN	_	2	_		)
t	Response time to external				1	tshrtimer <sup>(2</sup>
t <sub>LAT(DF)</sub>	synchronization request	_	_		'	)
	Pulse width on SHRTIMER_SCOUT			16	-	t <sub>SHRTIMER</sub> (2
t <sub>W(AF)</sub>	output					,
	F	f <sub>SHRTIMER</sub> = 180 MHz	_	88.89	_	ns

<sup>(1)</sup> Guaranteed by design, not tested in production.

### 4.25. TIMER characteristics

Table 4-60. TIMER characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit	
4	Times recolution time		1	1	t <sub>TIMERxCLK</sub>	
t <sub>res</sub>	Timer resolution time	f <sub>TIMERxCLK</sub> = 180 MHz	5.6	_	ns	
f	Timer external clock		0	f <sub>TIMERxCLK</sub> /2	MHz	
f <sub>EXT</sub>	frequency	f <sub>TIMERxCLK</sub> = 180 MHz	0	90	MHz	
RES	Times recolution	TIMERx (except TIMER1)	_	16	hit	
KES	Timer resolution	TIMER1	_	32	bit	
	16-bit counter clock period	_	1	65536	t <sub>TIMERxCLK</sub>	
	when internal clock is selected	f <sub>TIMERxCLK</sub> = 180 MHz	0.0056	364.1	μs	
tCOUNTER	32-bit counter clock period	_	1	2 <sup>32</sup>	t <sub>TIMERxCLK</sub>	
	when internal clock is selected (only TIMER1)	f <sub>TIMERxCLK</sub> = 180 MHz	0.0056	23.86	s	
	Maximum possible count		_	$2^{16} \times 2^{16}$	t <sub>TIMERxCLK</sub>	
t <sub>MAX_</sub> COUNT	( except TIMER1 )	f <sub>TIMERxCLK</sub> = 180 MHz	_	23.86	S	
	Maximum possible count	_		$2^{16} \times 2^{32}$	t <sub>TIMERxCLK</sub>	
	(only TIMER1)	f <sub>TIMERxCLK</sub> = 180 MHz	_	2 <sup>16</sup> x 23.86	s	

 $<sup>(1) \</sup>quad \hbox{Guaranteed by design, not tested in production.}$ 



### 4.26. WDGT characteristics

Table 4-61. FWDGT min/max timeout period at 40 kHz (IRC40K)(1)

Prescaler divider	PSC[2:0] bits	Min time out RLD[11:0] = 0x000	Max timeout RLD[11:0] = 0xFFF	Unit
1/4	000	0.025	409.525	
1/8	001	0.025	819.025	
1/16	010	0.025	1638.025	
1/32	011	0.025	3276.025	ms
1/64	100	0.025	6552.025	
1/128	101	0.025	13104.025	
1/256	110 or 111	0.025	26208.025	

<sup>(1)</sup> Guaranteed by design, not tested in production.

Table 4-62. WWDGT min-max timeout value at 90 MHz (f<sub>PCLK1</sub>)<sup>(1)</sup>

			7	,	
Prescaler divider	PSC[1:0]	Min timeout value CNT[6:0] = 0x40	Unit	Max timeout value CNT[6:0] = 0x7F	Unit
1/1	00	45.51		2.91	
1/2	01	91.02		5.83	
1/4	10	182.04	μs	11.65	ms
1/8	11	364.08		23.30	

<sup>(1)</sup> Guaranteed by design, not tested in production.

### 4.27. Parameter condition

Unless otherwise specified, all values given for  $V_{DD} = V_{DDA} = 3.3 \text{ V}$ ,  $T_A = 25 \,^{\circ}\text{C}$ .



#### 5. **Package information**

#### LQFP144 package outline dimensions 5.1.

DETAIL: F SECTION B-B

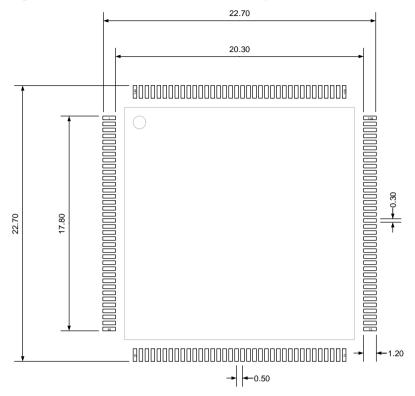
Figure 5-1. LQFP144 package outline

Table 5-1 I OFP144 package dimensions

Table 5-1. LQFP144 package dimensions						
Symbol	Min	Тур	Max			
А	_	_	1.60			
A1	0.05		0.15			
A2	1.35	1.40	1.45			
А3	0.59	0.64	0.69			
b	0.18		0.26			
b1	0.17	0.20	0.23			
С	0.13	_	0.17			
c1	0.12	0.13	0.14			
D	21.80	22.00	22.20			
D1	19.90	20.00	20.10			
Е	21.80	22.00	22.20			
E1	19.90	20.00	20.10			
е	_	0.50				
L	0.45	_	0.75			
L1	_	1.00	_			
θ	0°	_	7°			



Figure 5-2. LQFP144 recommended footprint





## 5.2. LQFP100 package outline dimensions

BASE METAL

SECTION B-B

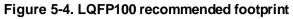
E1 E

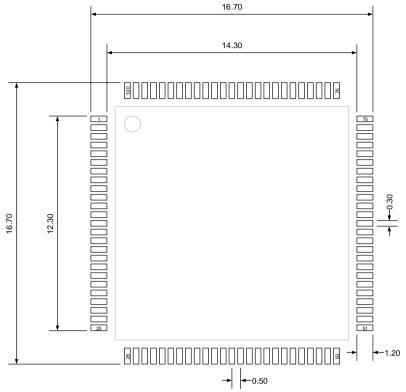
Figure 5-3. LQFP100 package outline

Table 5-2. LQFP100 package dimensions

Symbol	Min	Тур	Max
А	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
А3	0.59	0.64	0.69
b	0.18	_	0.26
b1	0.17	0.20	0.23
С	0.13	_	0.17
c1	0.12	0.13	0.14
D	15.80	16.00	16.20
D1	13.90	14.00	14.10
E	15.80	16.00	16.20
E1	13.90	14.00	14.10
е	_	0.50	_
eB	15.05	_	15.35
L	0.45	_	0.75
L1	_	1.00	_
θ	0°	_	7°









## 5.3. LQFP64 package outline dimensions

Figure 5-5. LQFP64 package outline

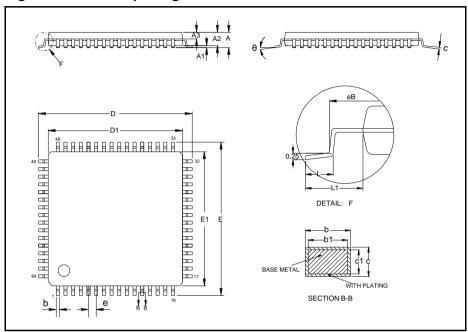
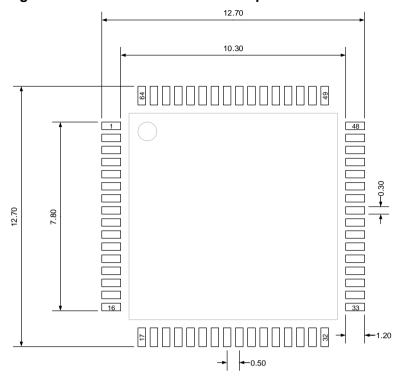


Table 5-3. LQFP64 package dimensions

Symbol	Min	Тур	Max
Α	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
A3	0.59	0.64	0.69
b	0.18		0.26
b1	0.17	0.20	0.23
С	0.13	_	0.17
c1	0.12	0.13	0.14
D	11.80	12.00	12.20
D1	9.90	10.00	10.10
E	11.80	12.00	12.20
E1	9.90	10.00	10.10
е	_	0.50	_
eB	11.25		11.45
L	0.45		0.75
L1	_	1.00	_
θ	0°		7°



Figure 5-6. LQFP64 recommended footprint





## 5.4. LQFP48 package outline dimensions

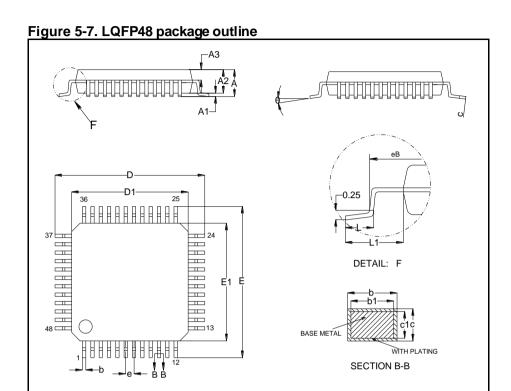


Table 5-4. LQFP48 package dimensions

Symbol	Min	Тур	Max
А	_	_	1.60
A1	0.05	_	0.15
A2	1.35	1.40	1.45
А3	0.59	0.64	0.69
b	0.18	_	0.26
b1	0.17	0.20	0.23
С	0.13	_	0.17
c1	0.12	0.13	0.14
D	8.80	9.00	9.20
D1	6.90	7.00	7.10
Е	8.80	9.00	9.20
E1	6.90	7.00	7.10
е	_	0.50	_
eB	8.10	_	8.25
L	0.45	_	0.75
L1	_	1.00	
θ	0°	_	7°

25



7.30

**-**0.50

Figure 5-8. LQFP48 recommended footprint

(Original dimensions are in millimeters)

12



#### 5.5. Thermal characteristics

Thermal resistance is used to characterize the thermal performance of the package device, which is represented by the Greek letter "0". For semiconductor devices, thermal resistance represents the steady-state temperature rise of the chip junction due to the heat dissipated on the chip surface.

 $\theta_{\text{JA}}$ : Thermal resistance, junction-to-ambient.

 $\theta_{JB}$ : Thermal resistance, junction-to-board.

 $\theta_{JC}$ : Thermal resistance, junction-to-case.

Ψ<sub>JB</sub>: Thermal characterization parameter, junction-to-board.

 $\Psi_{JT}$ : Thermal characterization parameter, junction-to-top center.

$$\theta_{JA} = (T_J - T_A)/P_D \tag{5-1}$$

$$\theta_{JB} = (T_J - T_B)/P_D \tag{5-2}$$

$$\theta_{JC} = (T_J - T_C)/P_D \tag{5-3}$$

Where,  $T_J$  = Junction temperature.

 $T_A$  = Ambient temperature

 $T_B$  = Board temperature

T<sub>C</sub> = Case temperature which is monitoring on package surface

P<sub>D</sub> = Total power dissipation

 $\theta_{JA}$  represents the resistance of the heat flows from the heating junction to ambient air. It is an indicator of package heat dissipation capability. Lower  $\theta_{JA}$  can be considerate as better overall thermal performance.  $\theta_{JA}$  is generally used to estimate junction temperature.

 $\theta_{\text{JB}}$  is used to measure the heat flow resistance between the chip surface and the PCB board.

 $\theta_{JC}$  represents the thermal resistance between the chip surface and the package top case.  $\theta_{JC}$  is mainly used to estimate the heat dissipation of the system (using heat sink or other heat dissipation methods outside the device package).

Table 5-5. Package thermal characteristics(1)

Symbol	Condition	Package	Value	Unit	
		LQFP144	48.76		
0	Natural convection, 2S2P PCB	LQFP100	49.18	°C/W	
$\theta_{JA}$	Natural Convection, 252F FCB	LQFP64	54.57		
		LQFP48	69.64		
		LQFP144	35.00		
θЈВ	Cold plate, 2S2P PCB	LQFP100	22.70	°C/W	
		LQFP64	35.08		



# GD32E503xxDatasheet

Symbol	Condition	Package	Value	Unit
		LQFP48	43.16	
		LQFP144	12.03	
$\theta_{ m JC}$	Cold plate, 2S2P PCB	LQFP100	12.52	°C/W
OJC	Colu plate, 232F FOB	LQFP64	18.11	C/VV
		LQFP48	25.36	
	Natural convection, 2S2P PCB	LQFP144	35.32	°C/W
		LQFP100	32.85	
$\Psi_{ m JB}$		LQFP64	35.41	
		LQFP48	47.75	
		LQFP144	1.86	
	Natural convection 252P PCP	LQFP100	0.53	°C/W
ΨJT	Natural convection, 2S2P PCB	LQFP64	1.10	
		LQFP48	2.45	

<sup>(1)</sup> Thermal characteristics are based on simulation, and meet JEDEC specification.



# 6. Ordering information

Table 6-1. Part ordering code for GD32E503xx devices

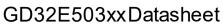
Ordering code	Flash (KB)	Package	Package type	Temperature operating range
GD32E503ZET6	512	LQFP144	Green	Industrial
GD32E3032E10	512	LQFF144	Green	-40°C to +85°C
GD32E503ZCT6	256	LQFP144	Green	Industrial
GD32E3032 C 10	250	LQFF144	Green	-40°C to +85°C
GD32E503V ET6	512	LQFP100	Green	Industrial
GD32E303 V E 10	512	LQFF100	Green	-40°C to +85°C
GD32E503VCT6	256	LQFP100	Green	Industrial
GD32E303 V C 16	230	LQFF100	G	-40°C to +85°C
GD32E503RET6	512	LQFP64	Green	Industrial
GD32E303RE16	512	LQFF04	G	-40°C to +85°C
GD32E503RCT6	256	LQFP64	Green	Industrial
GD32E303RC16	230	LQFF04	Green	-40°C to +85°C
GD32E503CET6	512	LQFP48	Green	Industrial
GD32E503CE16	512	LQFP46	Green	-40°C to +85°C
GD32E503CCT6	256	LQFP48	Green	Industrial
GLOZEOUSCCIO	200	LQFF40	Gleen	-40°C to +85°C
GD32E503CCT7	256	LQFP48	Green	Industrial
GD3ZE303CC17	200	LQFP40	Green	-40°C to +105°C



# 7. Revision history

Table 7-1. Revision history

Revision No.	Description	Date
1.0	Initial Release	Feb.28, 2020
1.1	<ol> <li>Module information modification, refers to <u>Func</u> <u>description</u>.</li> </ol>	Aug.28, 2020
	Modify boot pins in chapter <u>Boot modes</u> ;	
	2. Modify boot loader address in chapter <u>Memory</u>	<u>r map</u> ;
	3. Add deep-sleep 1 and deep-sleep 2 mode pow	er
1.2	consumption data, refers to Power consumption	<u>on</u> , and Dec.7, 2020
	modify the LDO mode conditions;	
	4. Electrical characteristics table update, refers to	<u>Electrical</u>
	<u>characteristics</u> .	
1.3	Add CAN module related information.	
	2. Modify I2C and SPI timing diagrams, refers to <u>I</u>	2 <u>C</u>
	characteristics and SPI characteristics.	Mar.24, 2021
	3. CAN module description modification, refers to	Controller
	area network (CAN).	
	Delete the OSCIN from PD0 remap information	in chapter
	2.6, and delete OSCOUT from PD1 remap infor	mation in
	chapter 2.6, and delete PD0 / PD1 from OSCIN	1
	OSCOUT remap information in chapter 2.6.3 ar	nd 2.6.4,
	delete ETM related functions in chapter 2.6, ref	ers to <u>Pin</u>
1.4	<u>definitions</u> .	D 44 0004
	2. Modify pinouts, refers to Pinouts and pin assignment	Dec.14, 2021
	3. Update SPI and I2S timing diagrams, refers to	<u>SPI</u>
	characteristics and 12S characteristics.	
	4. Update package information and ordering inform	mation,
	refers to <b>Package information</b> and <b>Ordering</b>	
	<u>information</u> .	
1.5	1. Add P <sub>D</sub> parameter in <u>Table 4-1. Absolute max</u>	imum_
	<u>ratings<sup>(1)(4)</sup></u> .	
	2. Add EMI parameter, refers to <i>Table 4-9. EMI</i>	
	<u>characteristics<sup>(1)</sup>.</u>	
	3. Modify LQFP64 package information, refer to <u>L</u>	<u>QFP64</u>
	package outline dimensions.	Jun.30, 2022
	<ol> <li>Update NRST external pin circuit, refer to <u>Figu</u></li> </ol>	re 4-4.
	Recommended external NRST pin circuit(1)	
	5. Change parameters in DC operating conditions,	refer to
	Table 42. DC operating conditions.	
	6. EXMC related pin update, refer to Pin definition	ons.





	1.	Pin name modification in <u>Pin definitions</u> and <u>Pinouts</u>		
1.6		and pin assignment.		
	2.	Add TRACESWO function to PB3 in Pindefinitions.		
	3.	Modify PA11 and PA12 to non-5V tolerant pin.		
	4.	Add comments to <b>Power consumption</b> .	Dec.6, 2022	
	5.	Modify I2C characteristics diagram Figure 4-6. I2C bus		
		<u>timing diagram</u> .		
	6.	Modify Table 5-1. LQFP144 package dimensions		
		parameter value.		
4.7	1.	Updated $V_{DD},V_{SSA},V_{DDA},V_{BAK} range$ from "1.62 to	Fab 00 0000	
1.7		3.6 V" to "1.71 to 3.63 V" in chapter 3.3.	Feb.28, 2023	
1.8	1.	The order information of GD32E503 CCT7 was added in	Apr.24, 2023	
1.8		chapter 6.		
1.9	1.	Fixed SPI max frequency from 30 MHz to 22.5MHz in		
		chapter 3.13.	lul 44 - 2022	
	2.	Operation temperature range -40 to +105°C added for	Jul.11, 2023	
		grade 7 devices.		



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